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50-500 GHZ Wireless: Transistors, ICs, and System Design

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Munkyo Seo, Jonathan Hacker, Adam Young, Zach Griffith, Richard Pierson, Miguel Urteaga, ***Teledyne Scientific Company***

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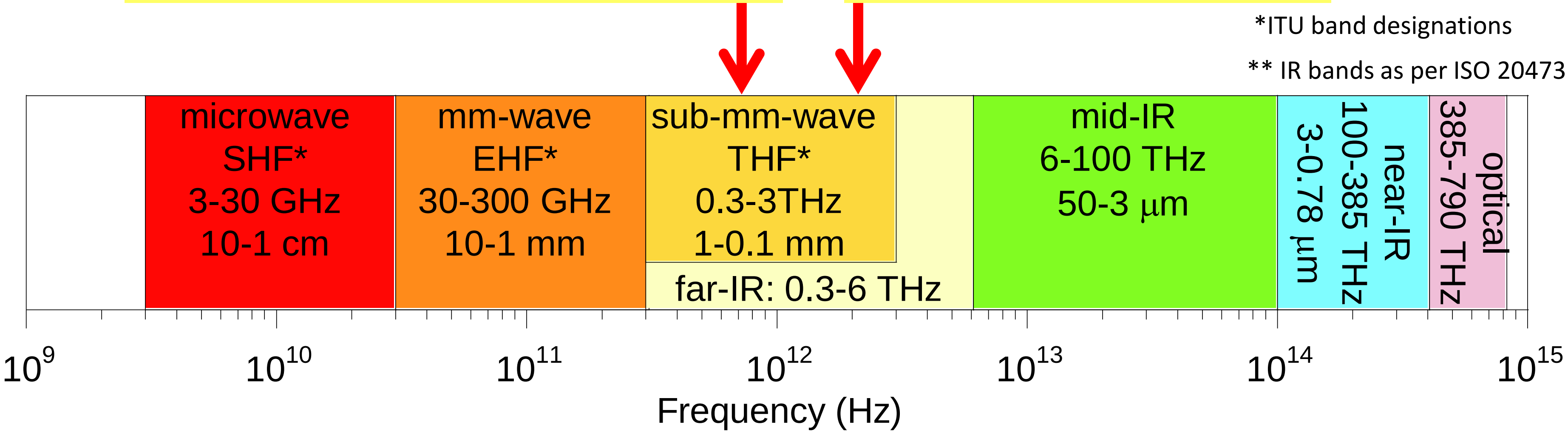
50-500 GHz Electronics: What Is It For ?

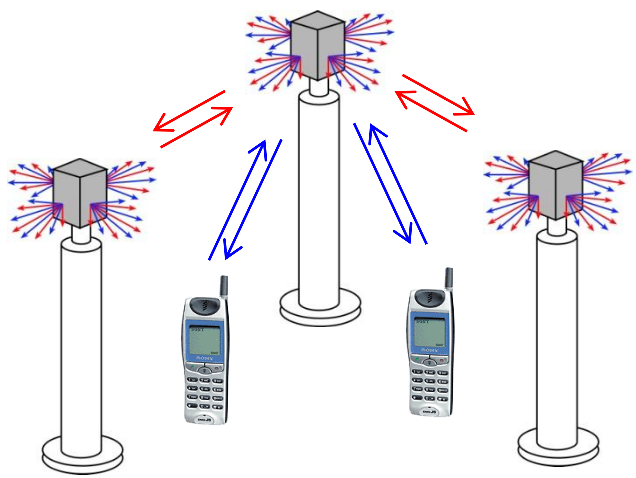
820 GHz transistor ICs today

2 THz clearly feasible

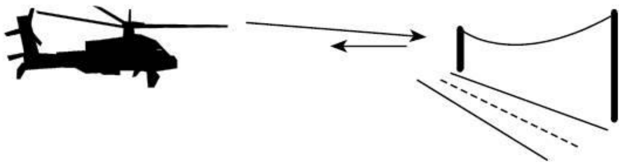


Applications

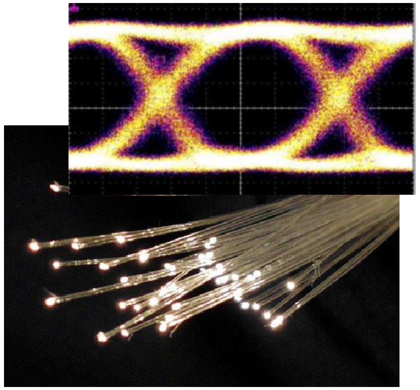
100+ Gb/s wireless networks



Video-resolution radar
→ fly & drive through fog & rain

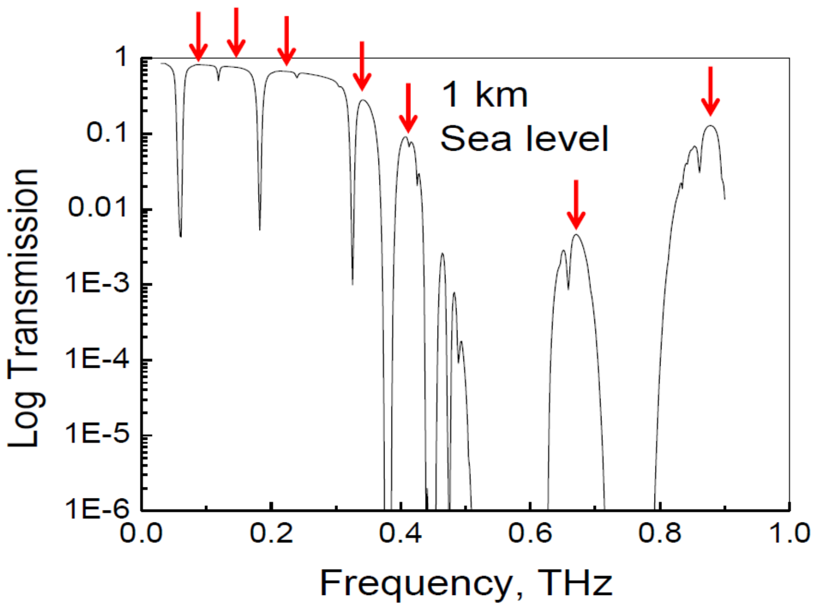


near-Terabit
optical fiber links



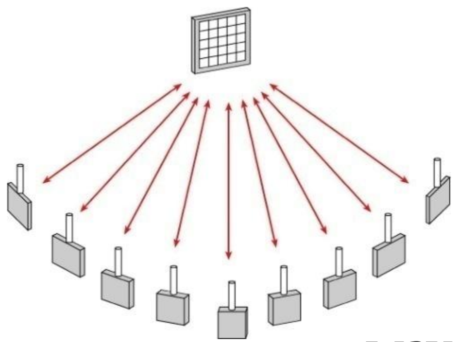
50-500 GHz Wireless Has High Capacity

very large bandwidths available

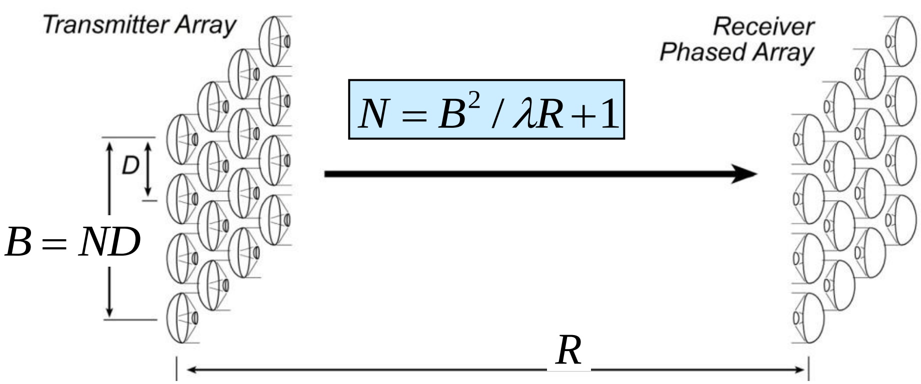


short wavelengths→ many parallel channels

Sheldon IMS 2009
Torkildson : IEEE Trans Wireless Comms. Dec. 2011.



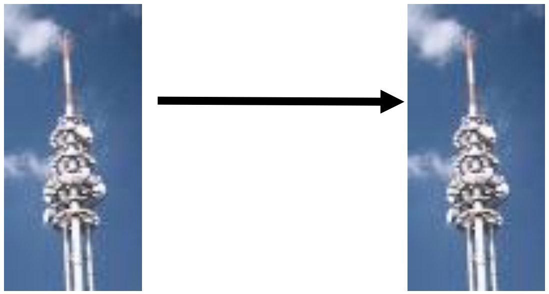
$$\text{angular resolution} \approx \frac{\text{wavelength}}{\text{array width}}$$



$$\#\text{channels} \propto (\text{aperture area})^2 / (\text{wavelength} \cdot \text{distance})^2$$

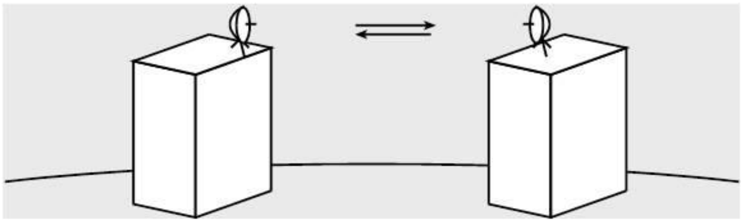
50-500 GHz Wireless Needs Phased Arrays

isotropic antenna → weak signal → short range



$$\left(\frac{P_{received}}{P_{transmitted}}\right) \propto \left(\frac{\lambda^2}{R^2}\right) e^{-\alpha R}$$

highly directional antenna → strong signal, but must be aimed

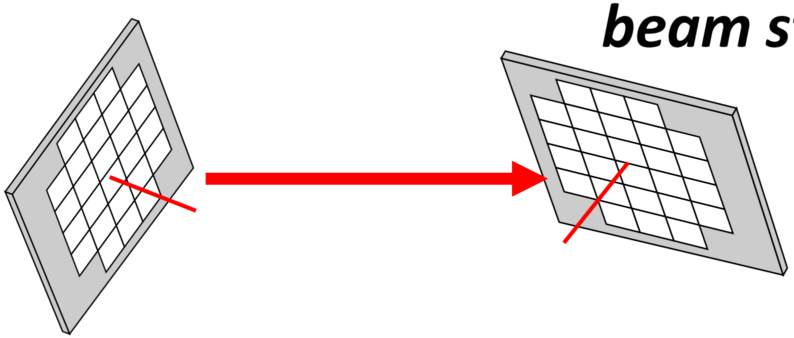


$$\left(\frac{P_{received}}{P_{transmitted}}\right) \propto D_t D_r \left(\frac{\lambda^2}{R^2}\right) e^{-\alpha R}$$

no good for mobile

must be precisely aimed → too expensive for telecom operators

beam steering arrays → strong signal, steerable

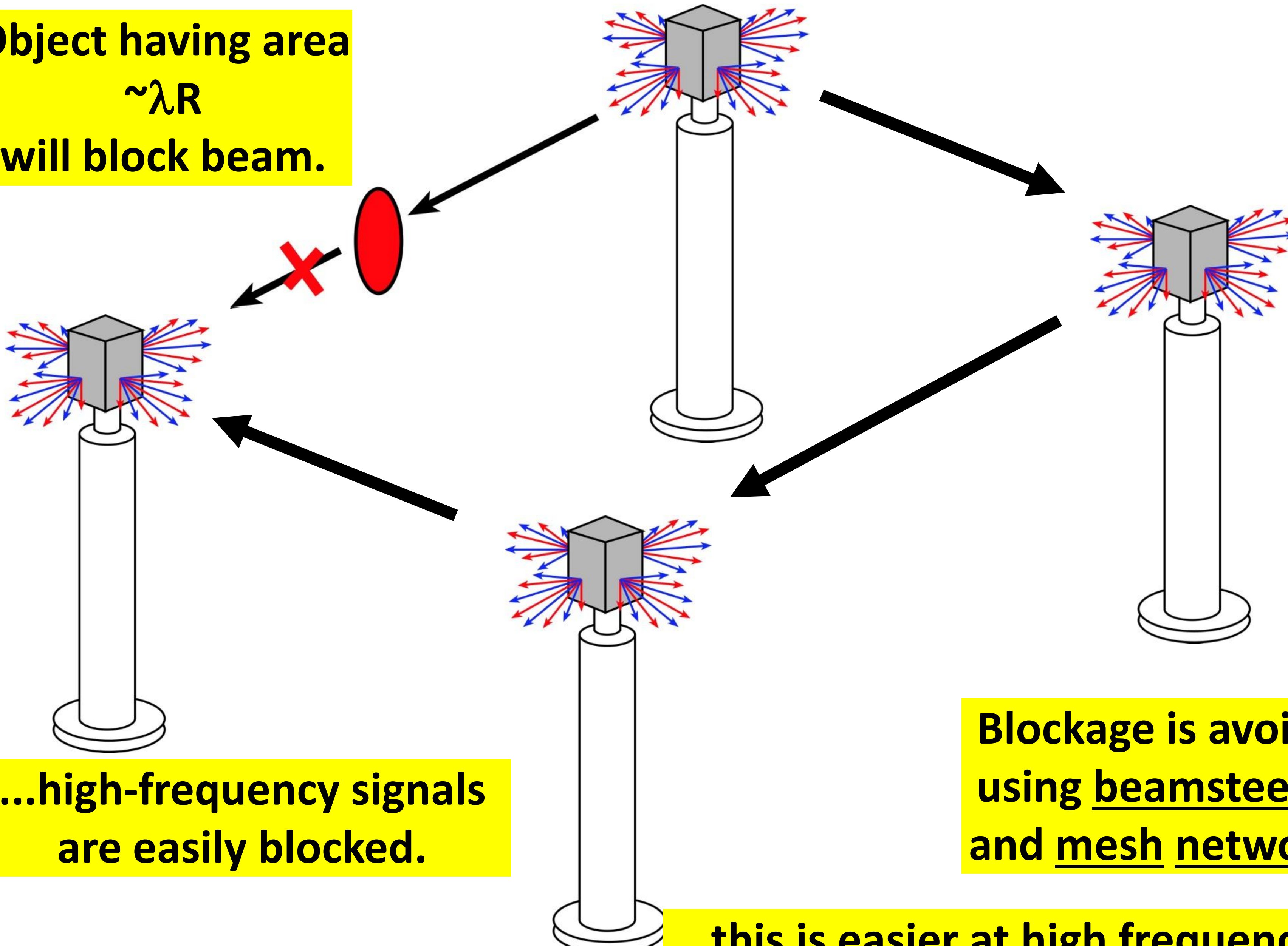


$$\frac{P_{received}}{P_{transmit}} \propto N_{receive} N_{transmit} \frac{\lambda^2}{R^2} e^{-\alpha R}$$

32-element array → 30 (45?) dB increased SNR

50-500 GHz Wireless Needs Mesh Networks

Object having area $\sim\lambda R$ will block beam.



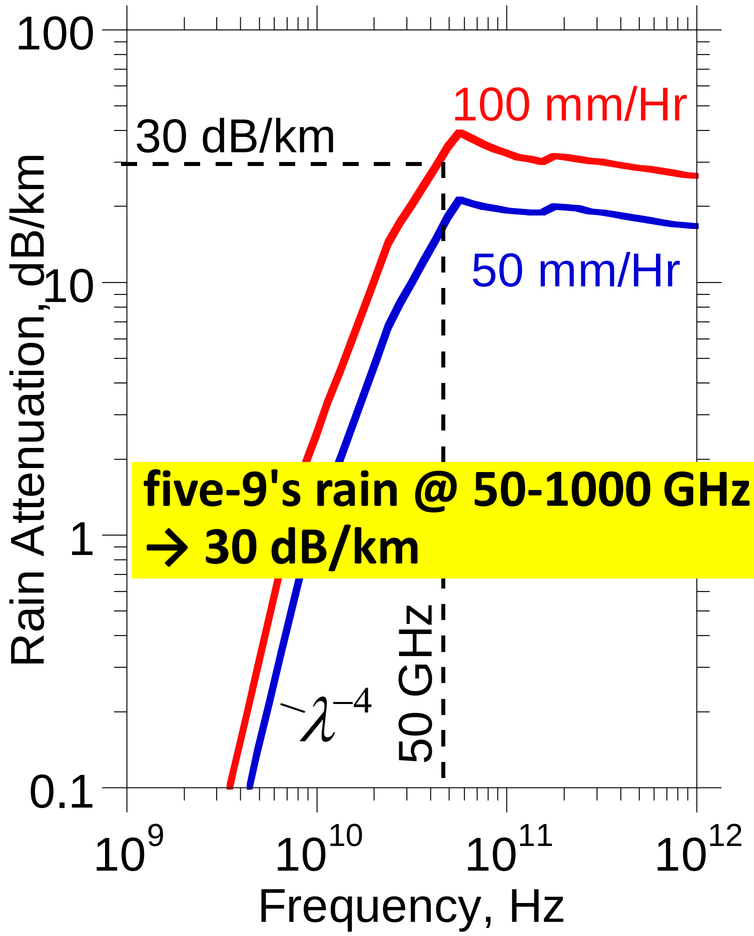
...high-frequency signals are easily blocked.

Blockage is avoided using <u>beamsteering</u> and <u>mesh</u> <u>networks</u>.

...this is easier at high frequencies.

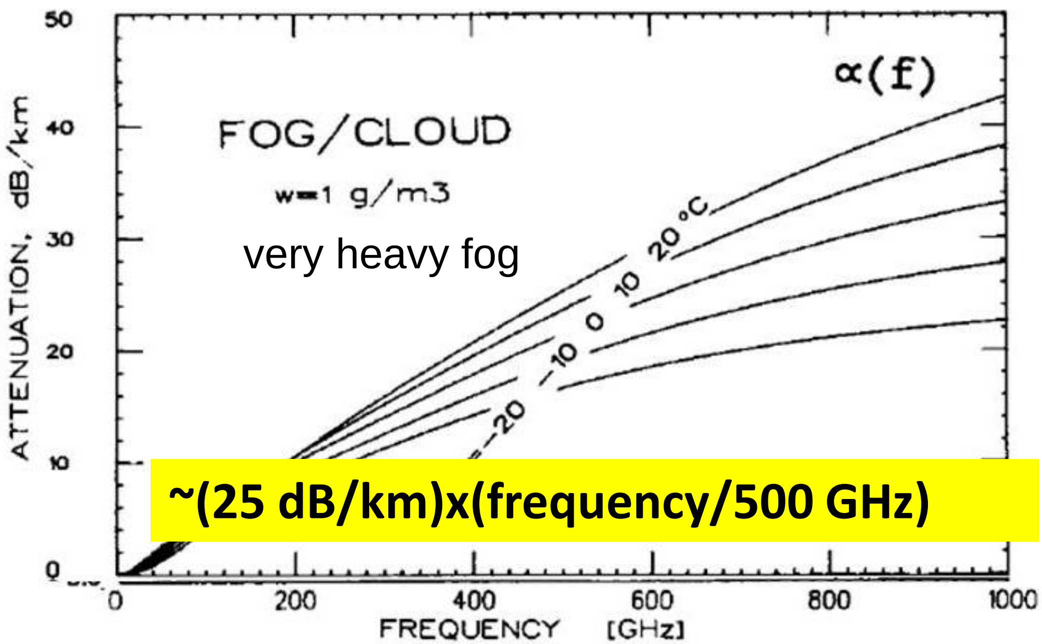
50-500 GHz Wireless Has High Attenuation

High Rain Attenuation



five-9's rain @ 50-1000 GHz:
→ 30 dB/km

High Fog Attenuation



~(25 dB/km)x(frequency/500 GHz)

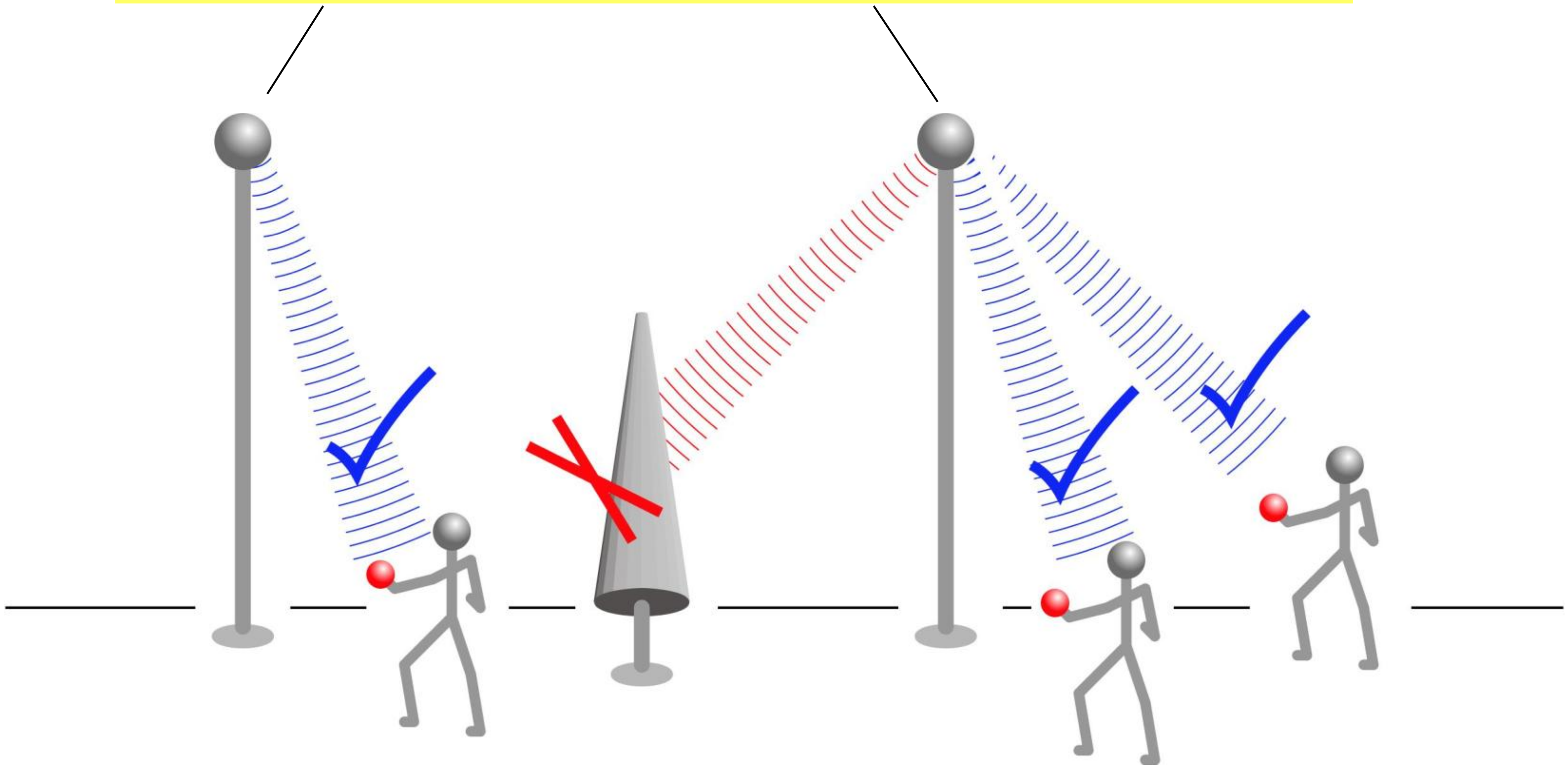
50-500 GHz links must tolerate ~30 dB/km attenuation

Olsen, Rogers, Hodge, IEEE Trans Antennas & Propagation Mar 1978 Liebe, Manabe, Hufford, IEEE Trans Antennas and Propagation, Dec. 1989

mm-Waves for Terabit Mobile Communications

Goal: ***1Gb/s per mobile user***

spatially-multiplexed mm-wave base stations



mm-Waves for Terabit Mobile Communications

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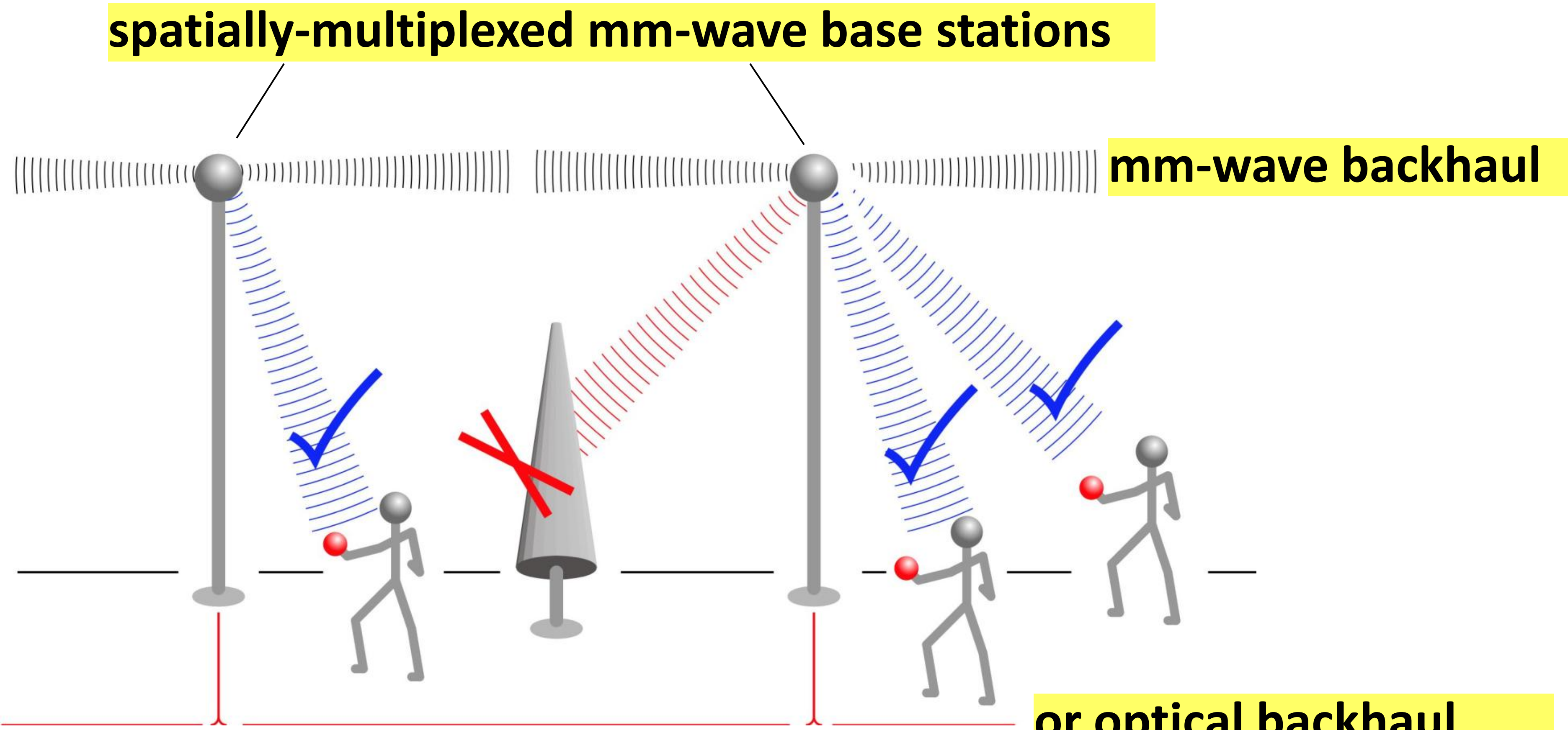
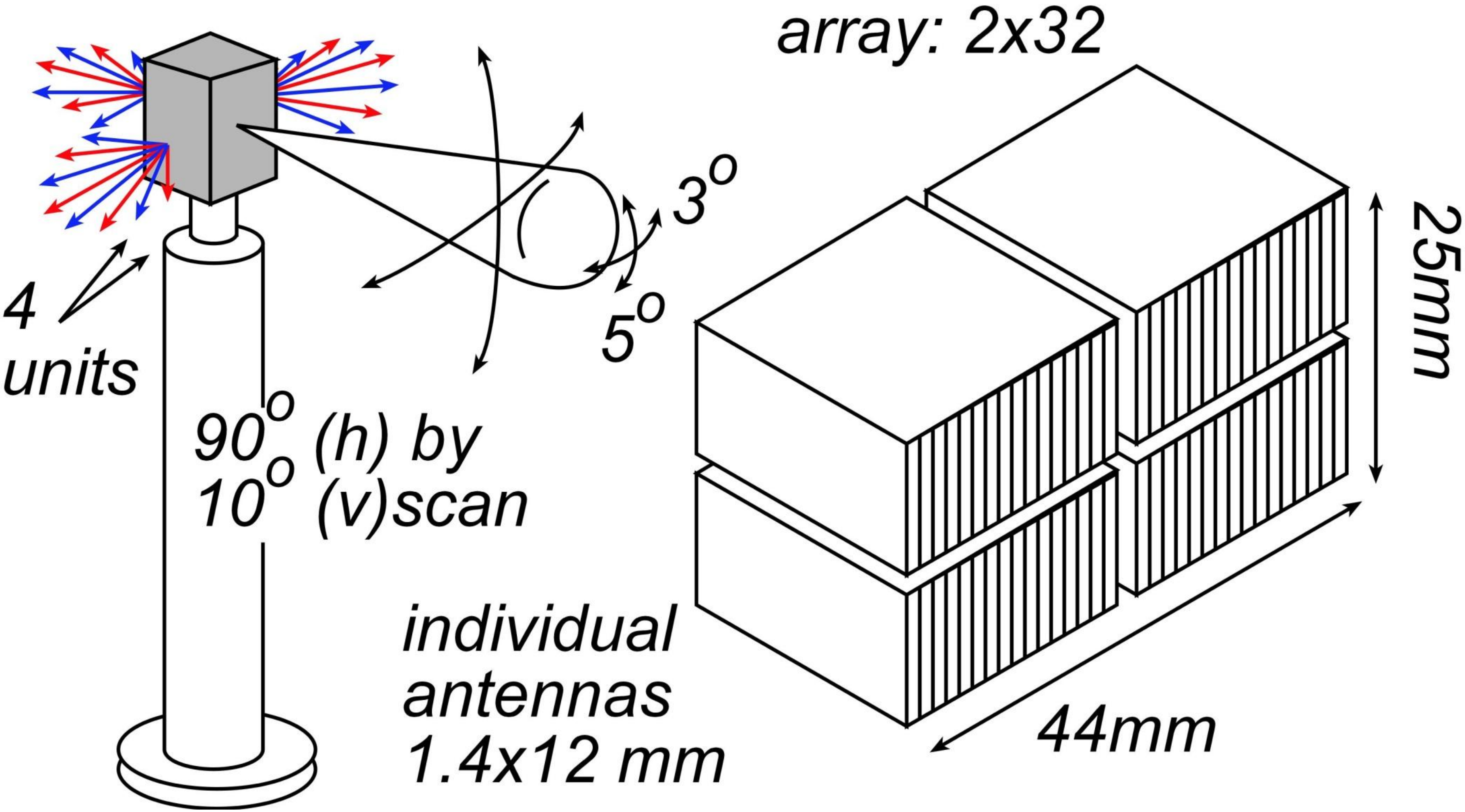
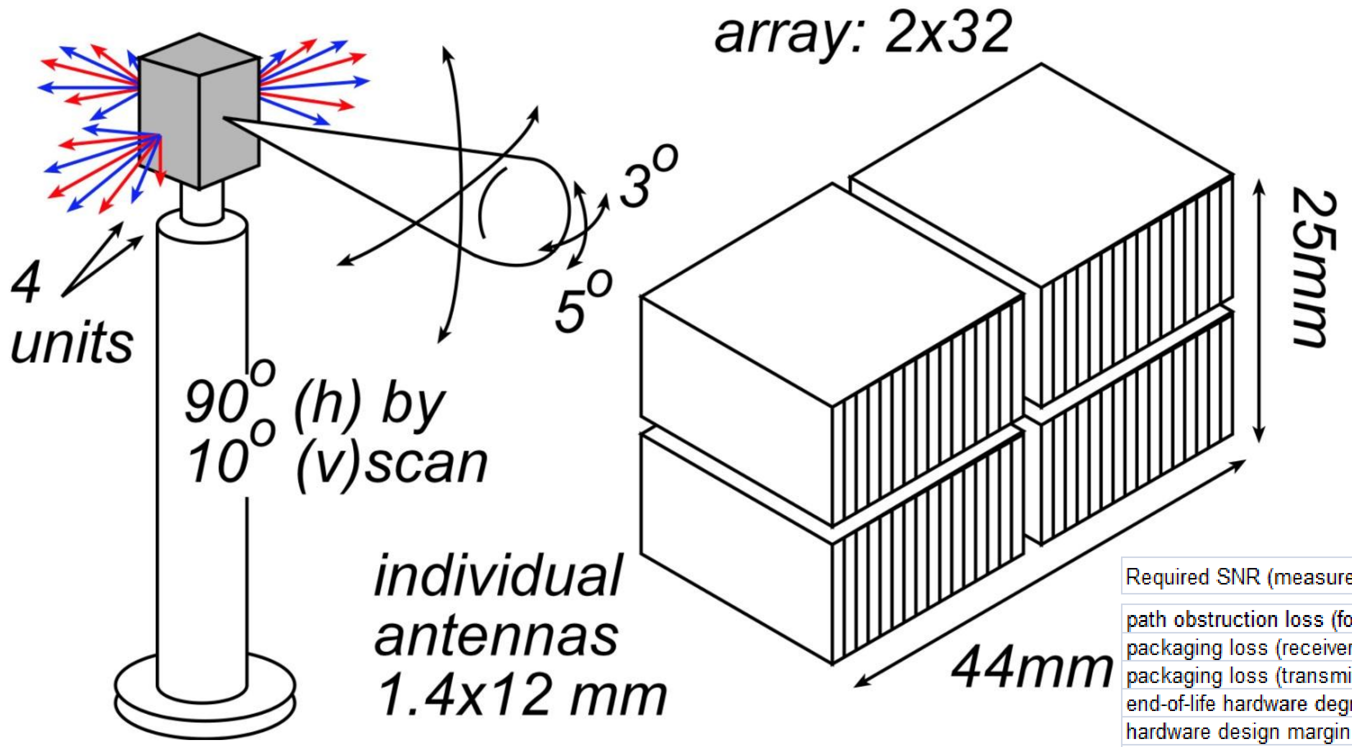


140 GHz, 10 Gb/s Adaptive Picocell Backhaul



140 GHz, 10 Gb/s Adaptive Picocell Backhaul



Required SNR (measured as Eb/No)	6.8	dB
path obstruction loss (foliage, glass)	5.00	dB
packaging loss (receiver)	3	dB
packaging loss (transmitter)	3	dB
end-of-life hardware degradation	3	dB
hardware design margin	3	dB
beam aiming loss (edge of beam)	3	dB
systems operating margin	10	dB
PA backoff for OFDM	7.00E+00	dB

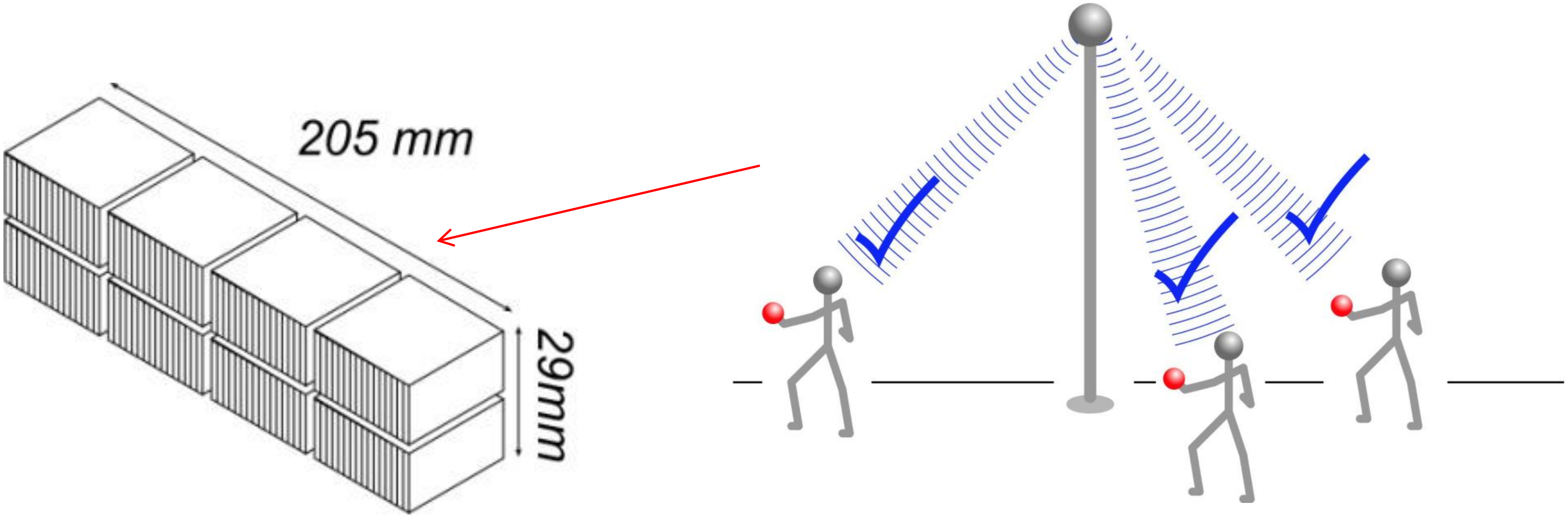
350 meters range in five-9's rain

Realistic packaging loss, operating & design margins

PAs: 24 dBm P_{sat} (per element)→ GaN or InP

LNAs: 4 dB noise figure → InP HEMT

60 GHz, 1 Tb/s Spatially-Multiplexed Base Station



2x64 array on each of four faces.

Each face supports 128 users, 128 beams: 512 total users.

Each beam: 2Gb/s.

200 meters range in 50 mm/hr rain

Realistic packaging loss, operating & design margins

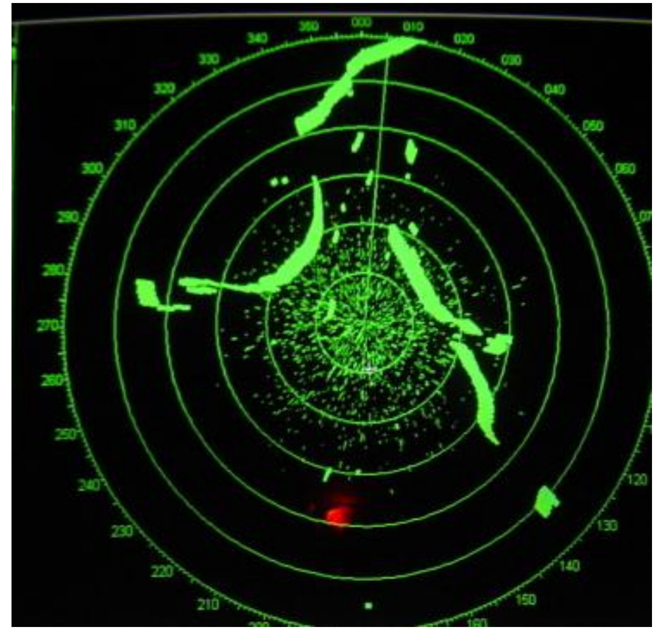
PAs: 20 dBm P_{out} , 26 dBm P_{sat} (per element)

LNAs: 3 dB noise figure

400 GHz frequency-scanned imaging radar

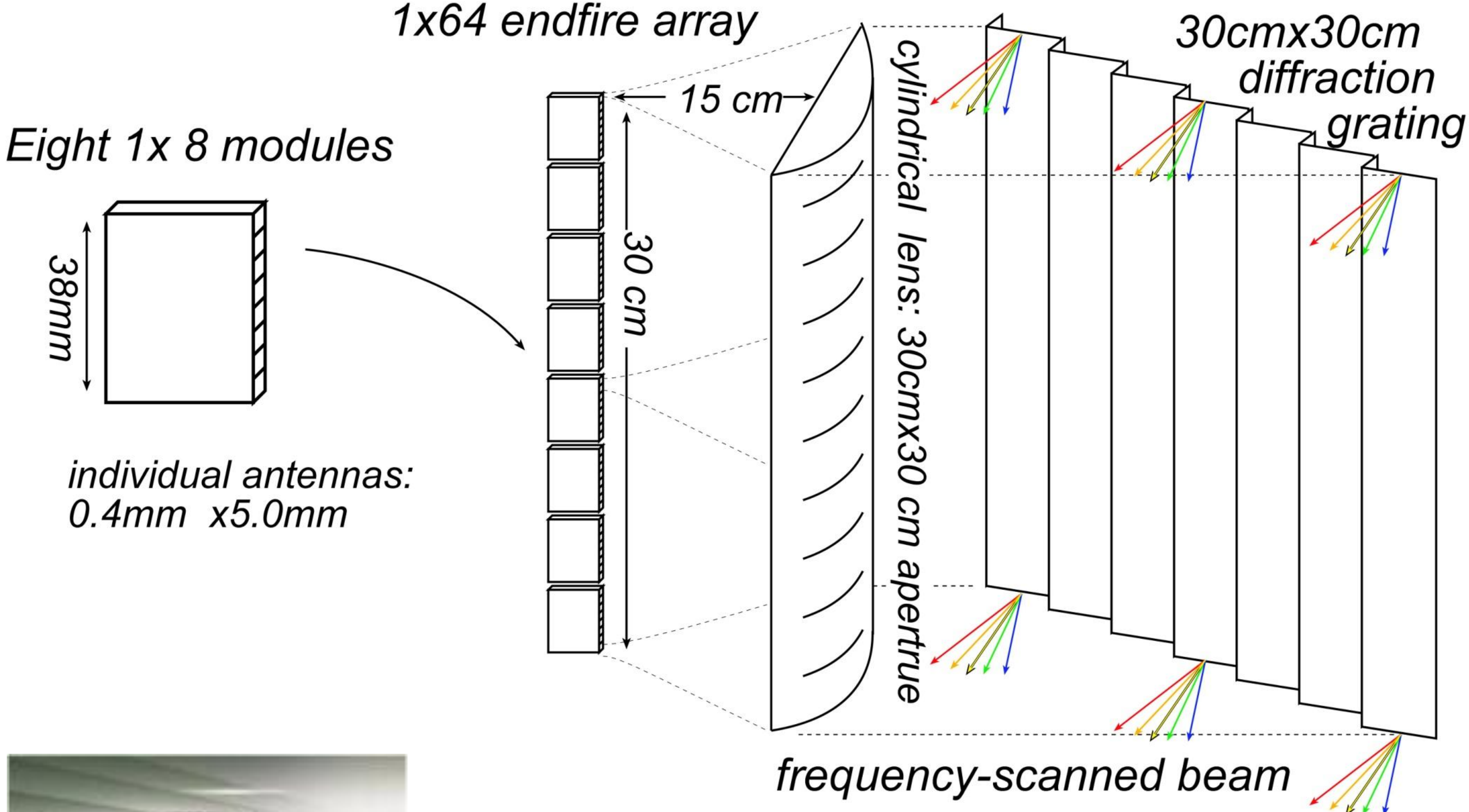
What your eyes see-- in fog

What you see with X-band radar



What you would like to see

400 GHz frequency-scanned imaging car radar

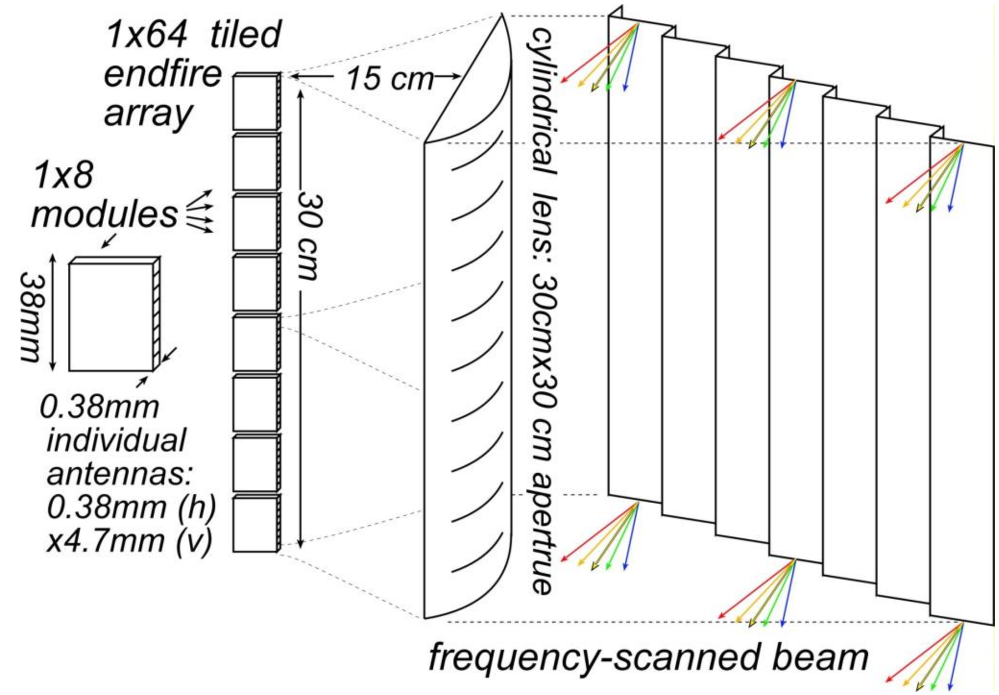


400 GHz frequency-scanned imaging car radar

Range: see a football at 300 meters (10 seconds warning) in heavy fog
(10 dB SNR, 25 dB/km, 30cm diameter target, 10% reflectivity, 100 km/Hr)

Image refresh rate: 60 Hz

Resolution 64×512 pixels



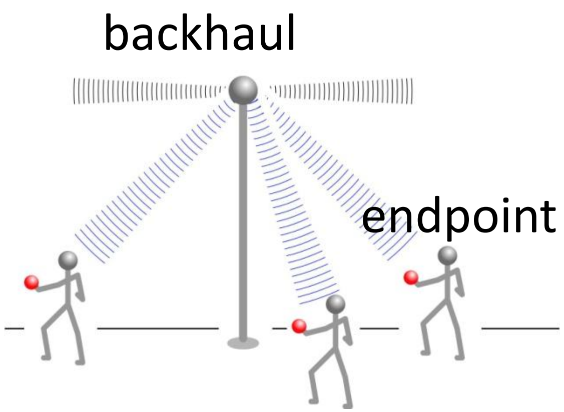
Angular resolution: 0.14 degrees

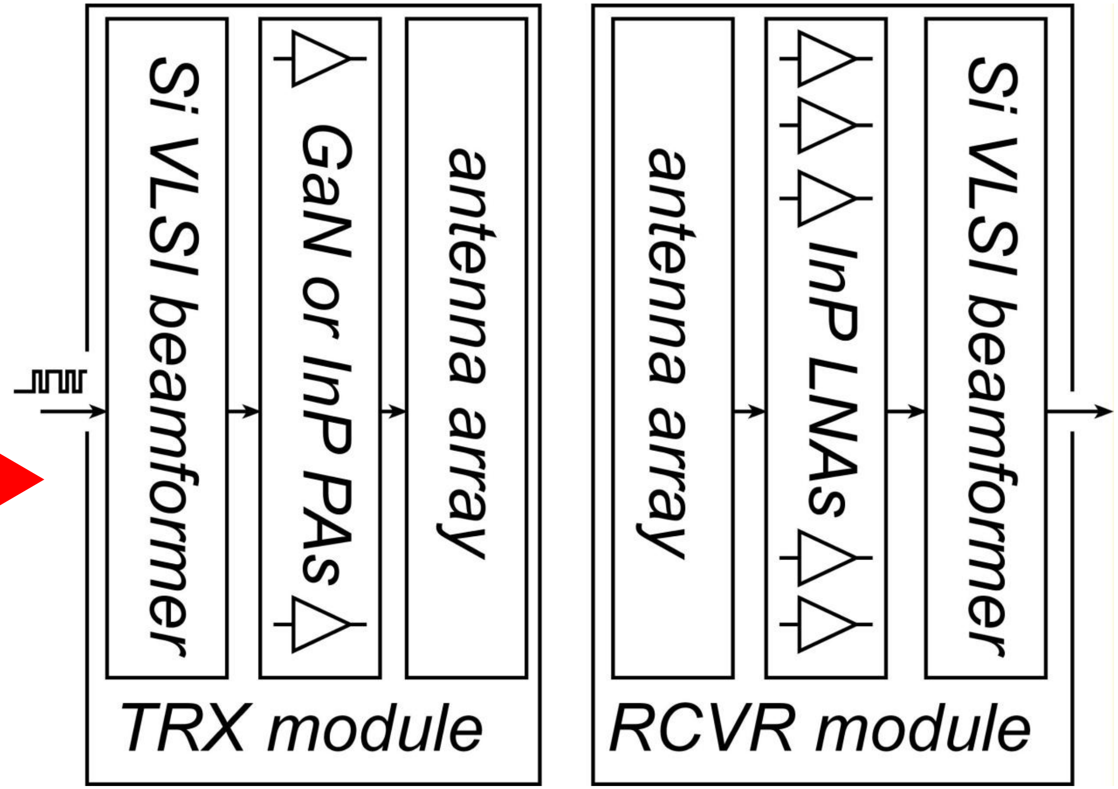
Angular field of view: 9 by 73 degrees

Aperture: 35 cm by 35 cm

Component requirements:
50 mW peak power/element,
3% pulse duty factor
6.5 dB noise figure,
5 dB package losses
5 dB manufacturing/aging margin

50-500 GHz Wireless Transceiver Architecture



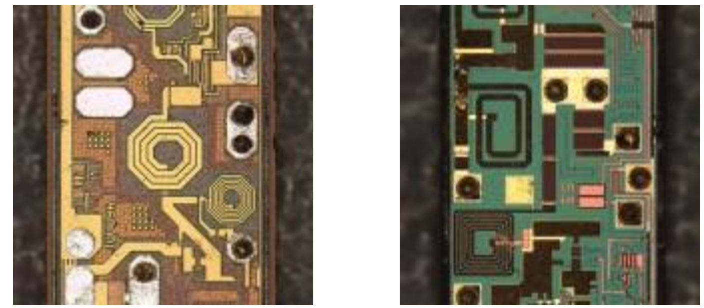


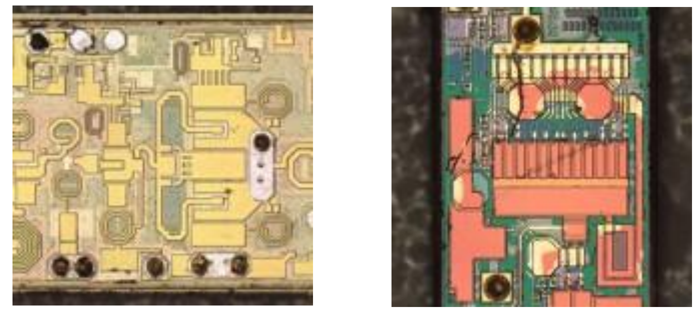
III-V LNAs, III-V PAs → power, efficiency, noise
Si CMOS beamformer→ integration scale

...similar to today's cell phones.

High antenna array gain → large array area
→ far too large for monolithic integration

III-V PAs and LNAs in today's wireless systems...



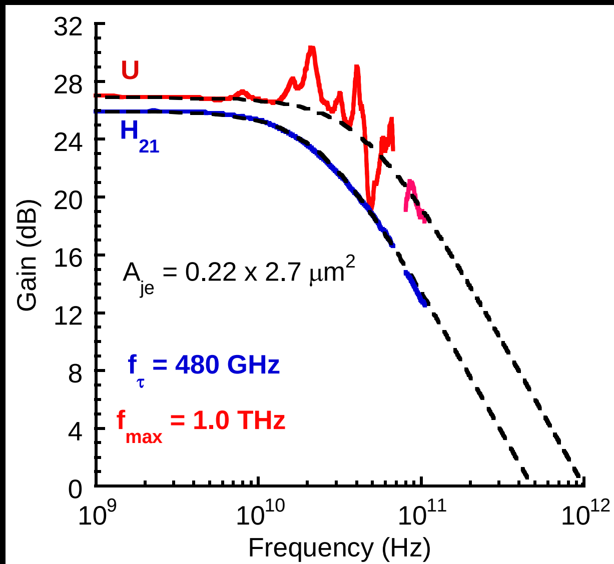


http://www.chipworks.com/blog/recentteardowns/2012/10/02/apple-iphone-5-the-rf/

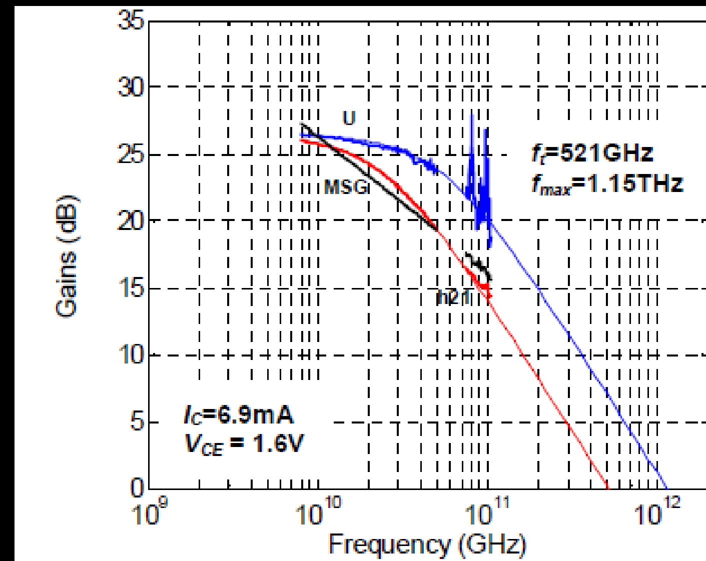
Transistors for 50-500 GHz systems

THz InP HBTs: Performance @ 130 nm Node

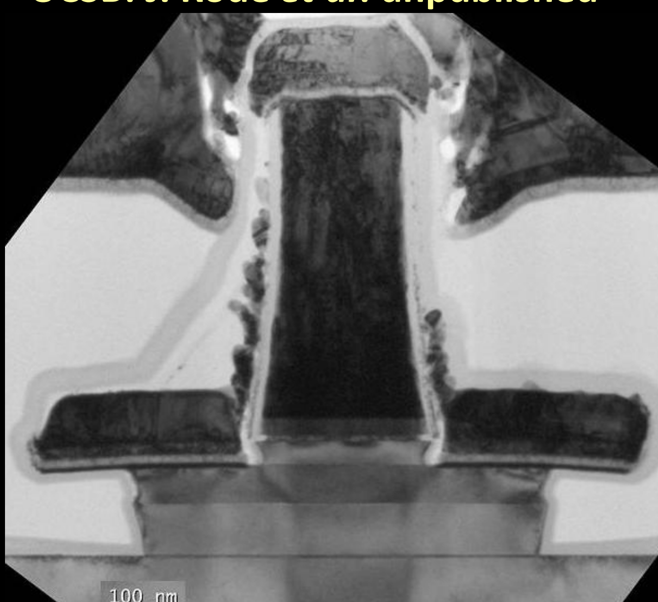
UCSB: V. Jain *et al*: 2011 DRC

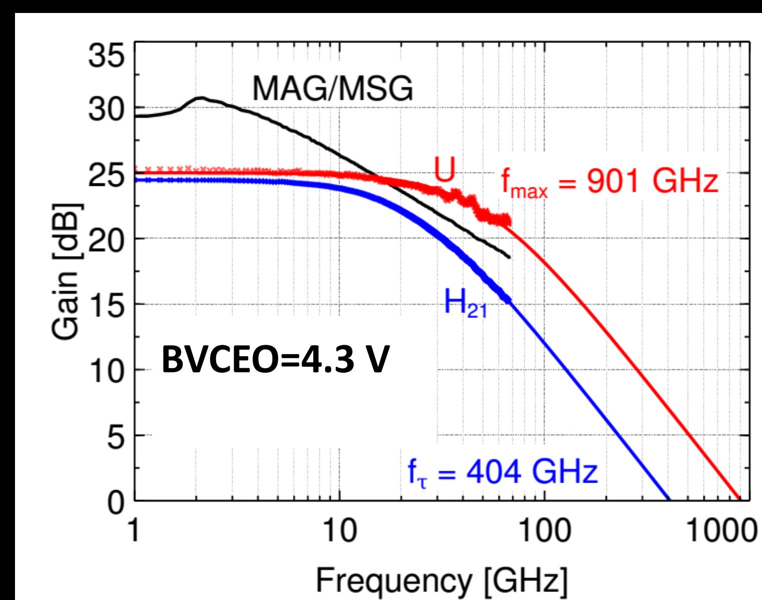


Teledyne: M. Urteaga *et al*: 2011 DRC



UCSB: J. Rode *et al*: unpublished





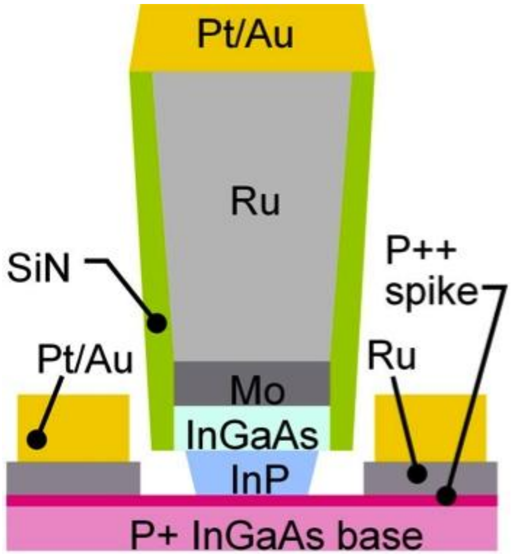
3-4 THz Bipolar Transistors are Feasible.

Needs:

very low resistivity contacts

very high current densities

narrow junctions



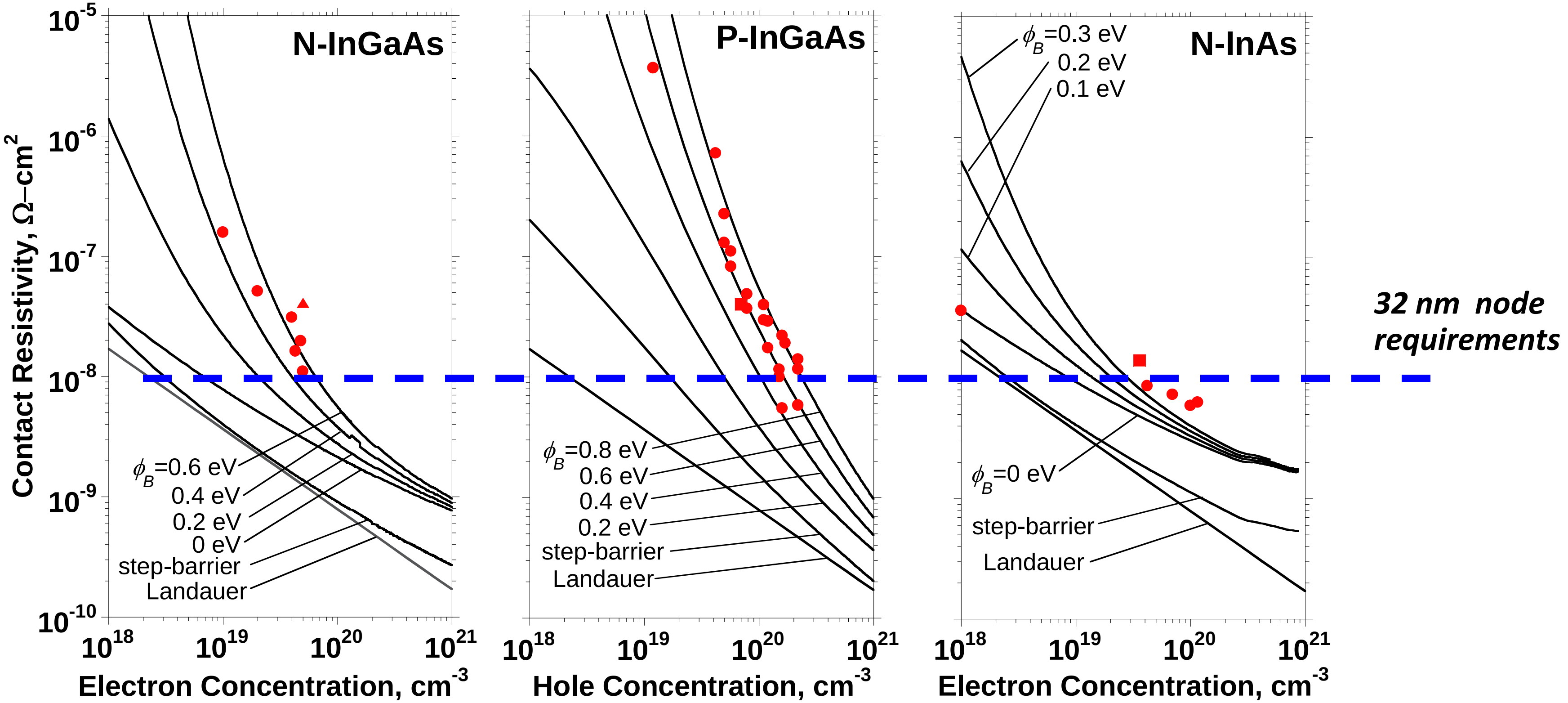
Impact:

Efficient power amplifiers, complex signal processing from 100-1000 GHz.

Scaling Node	64	32	16	nm
Emitter Width	64	32	16	nm
Resistivity	2	1	0.5	Ω-μm^2
Base Thickness	18	15	13	nm
Contact width	60	30	15	nm
Contact ρ	2.5	1.25	0.63	Ω-μm^2
Collector Width	180	90	45	nm
Thickness	53	37.5	26	nm
Current Density	36	72	140	mA/μm^2
f_τ	1.0	1.4	2.0	THz
f_{max}	2.0	2.8	4.0	THz

Ultra Low-Resistivity Refractory Contacts

Baraskar *et al*, Journal of Applied Physics, 2013

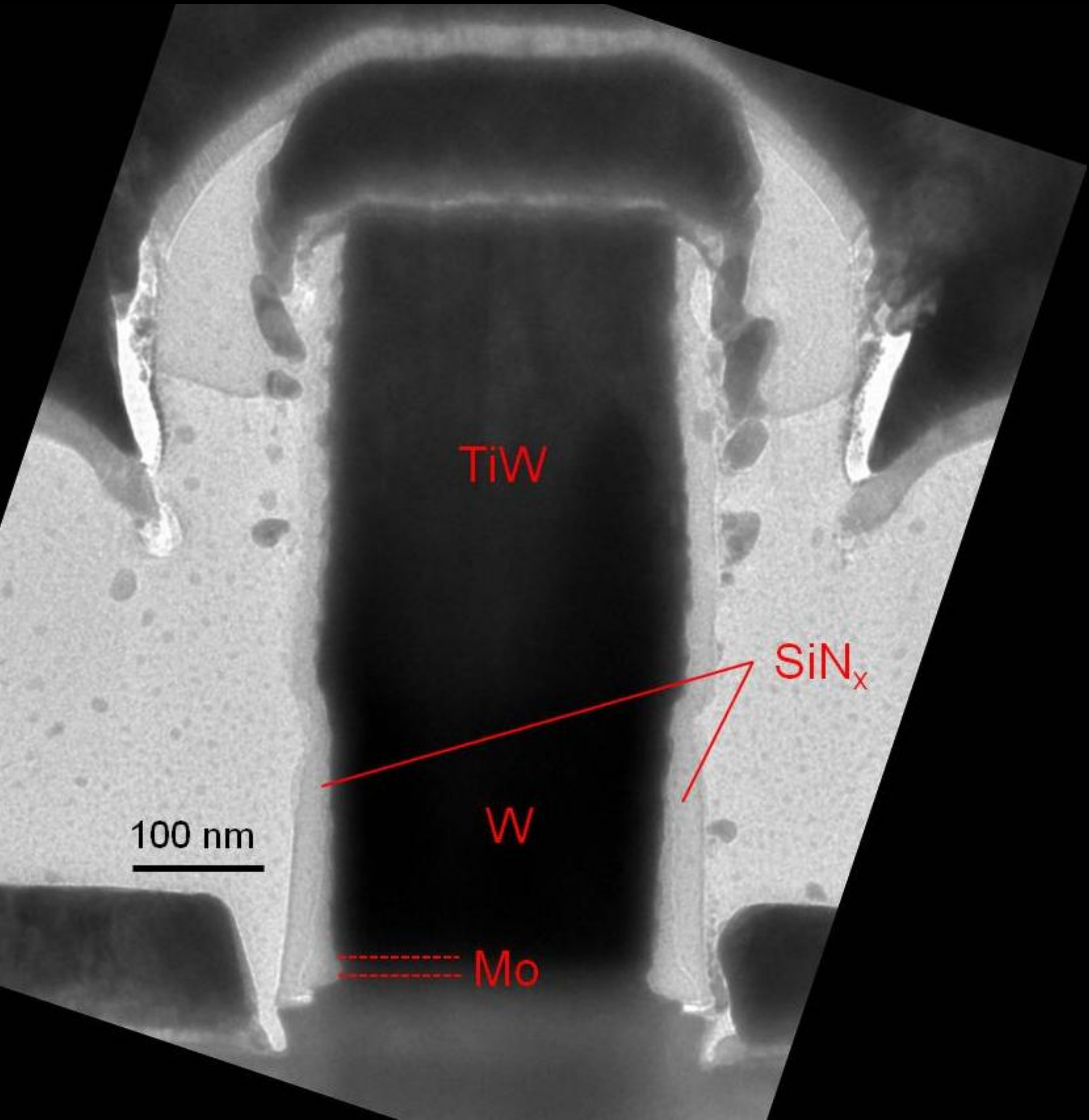


Refractory: robust under high-current operation.

Low penetration depth: ~ 1 nm.

Performance sufficient for 32 nm /2.8 THz node.

Refractory Emitter Contact and Via

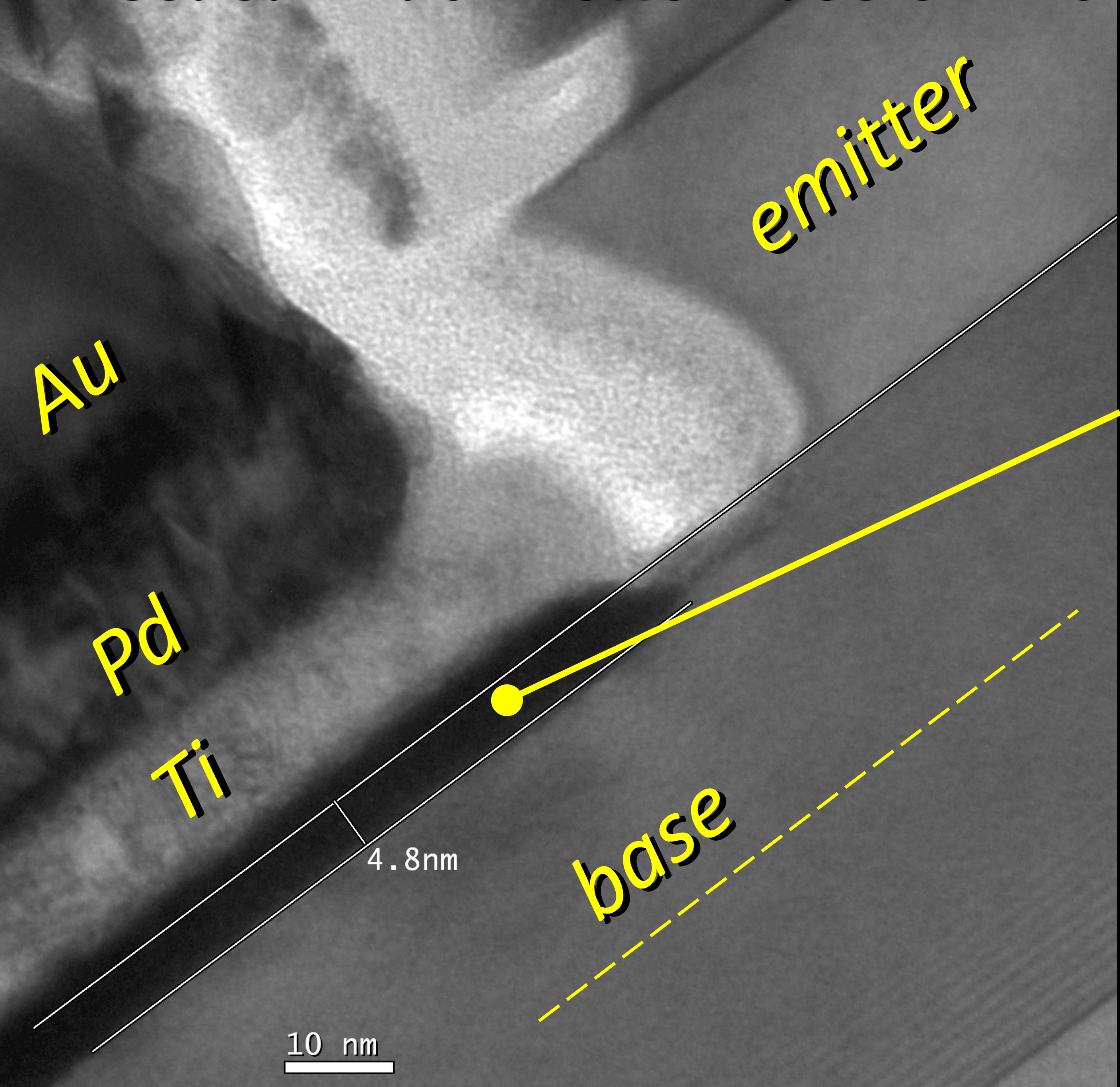


low-resistivity Mo contact

sputtered, dry-etched W/TiW via

Refractory metals→ high currents

Needed: Much Better Base Ohmic Contacts



Pt/Ti/Pd/Au

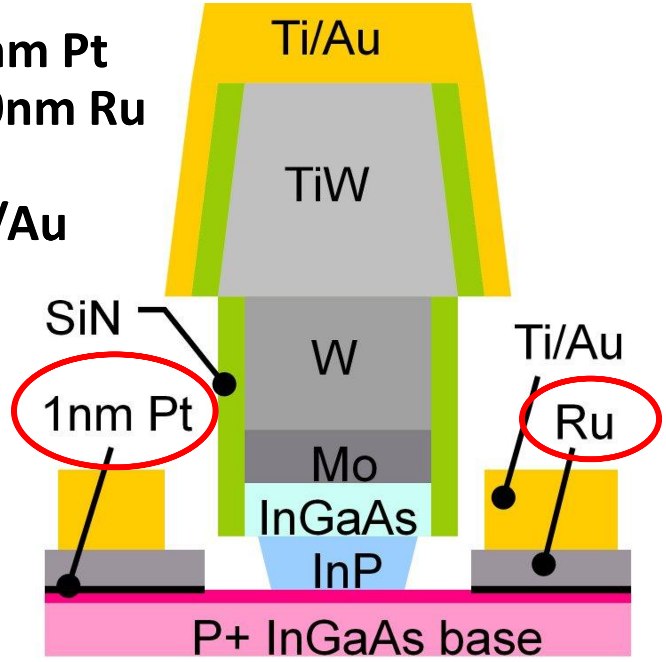
(3.5/12/17/70 nm)

~5 nm deep Pt contact reaction

(into 25 nm base)

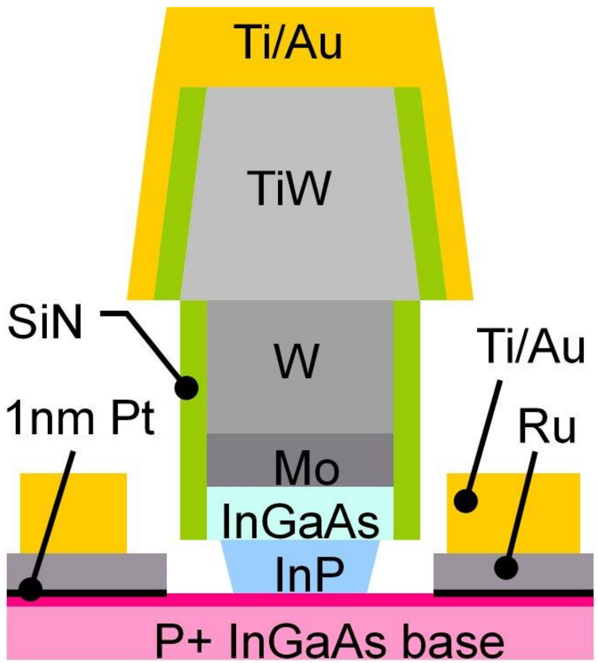
Two-Step Base Contact Process

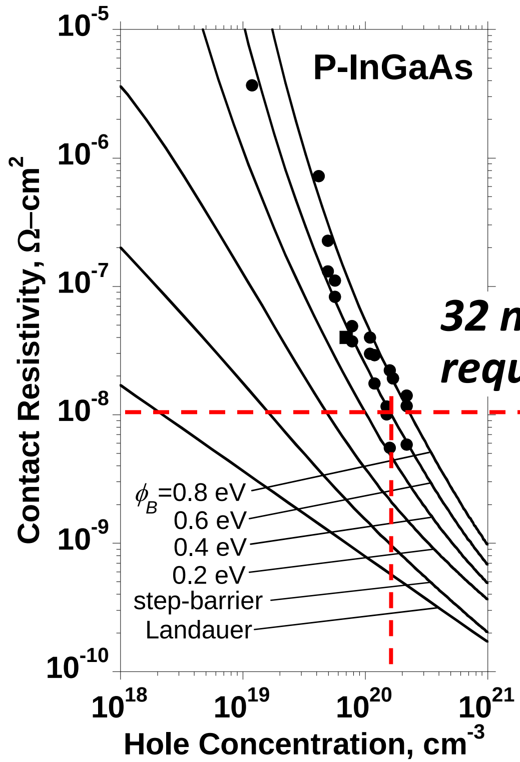
1) Blanket deposit 1nm Pt
2) Blanket deposit 10nm Ru (refractory)
3) Pattern deposit Ti/Au



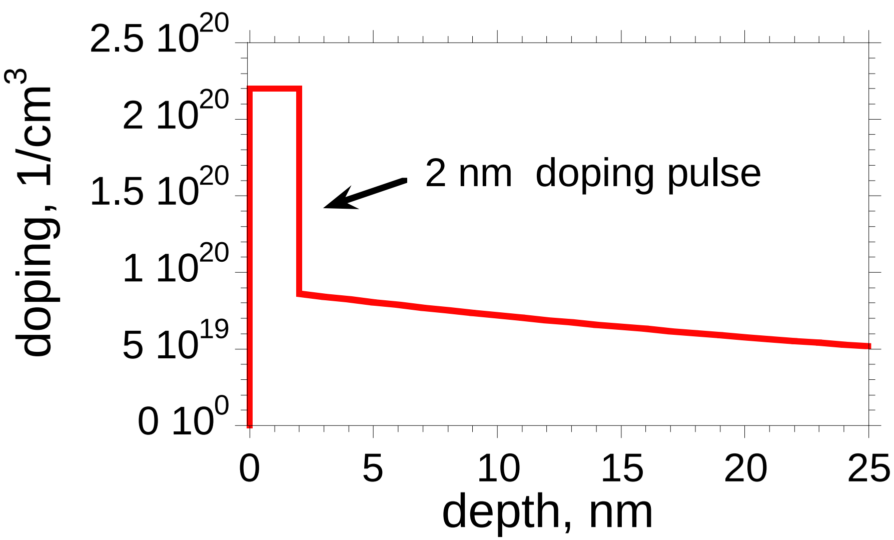
Surface not exposed to photoresist→ less surface contamination
1 nm Pt layer: 2-3 nm surface penetration
Thick Au: low metal resistance

Two-Step Base Contact Process





32 nm node requirement

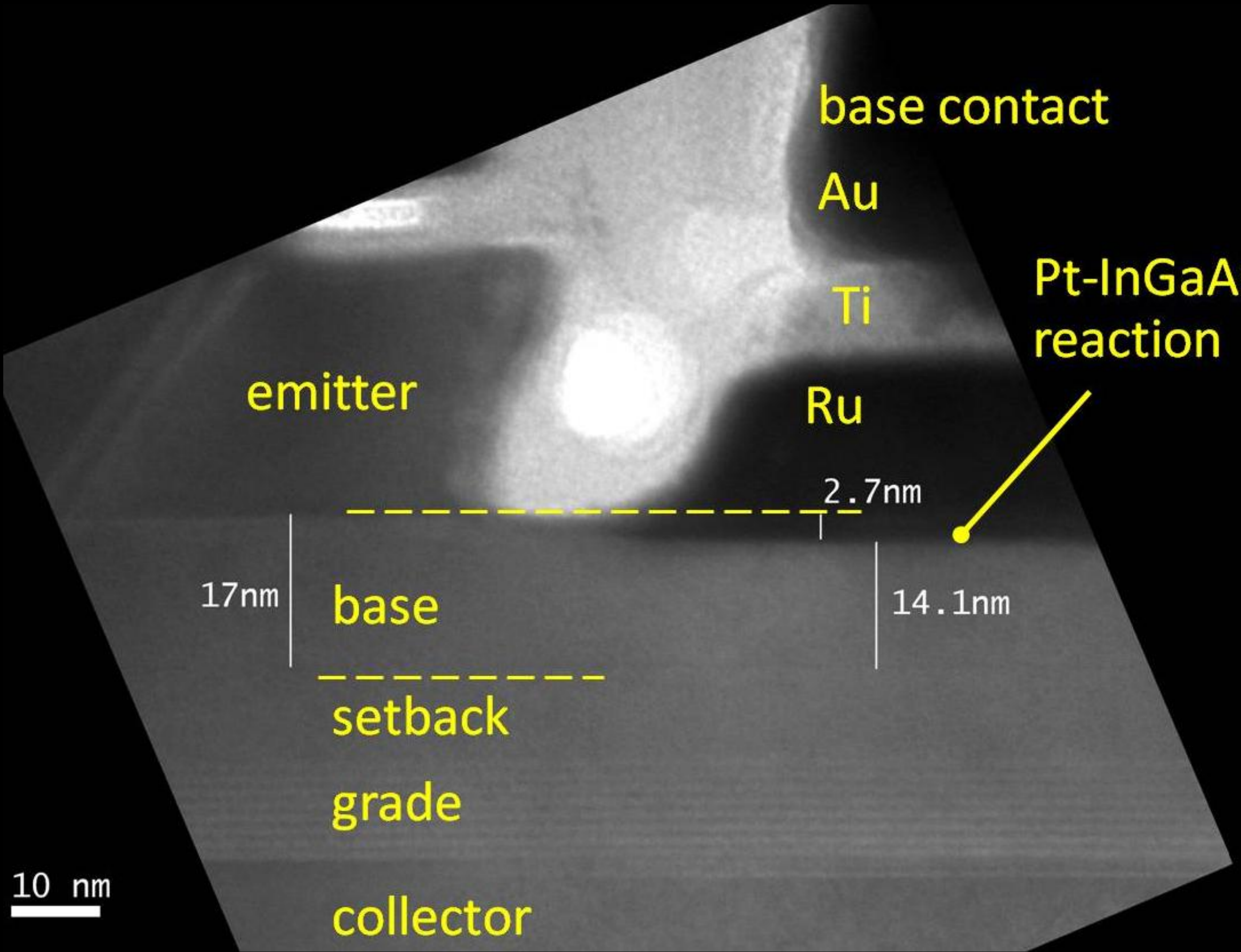


Increased surface doping:
reduced contact resistivity,
increased Auger recombination.

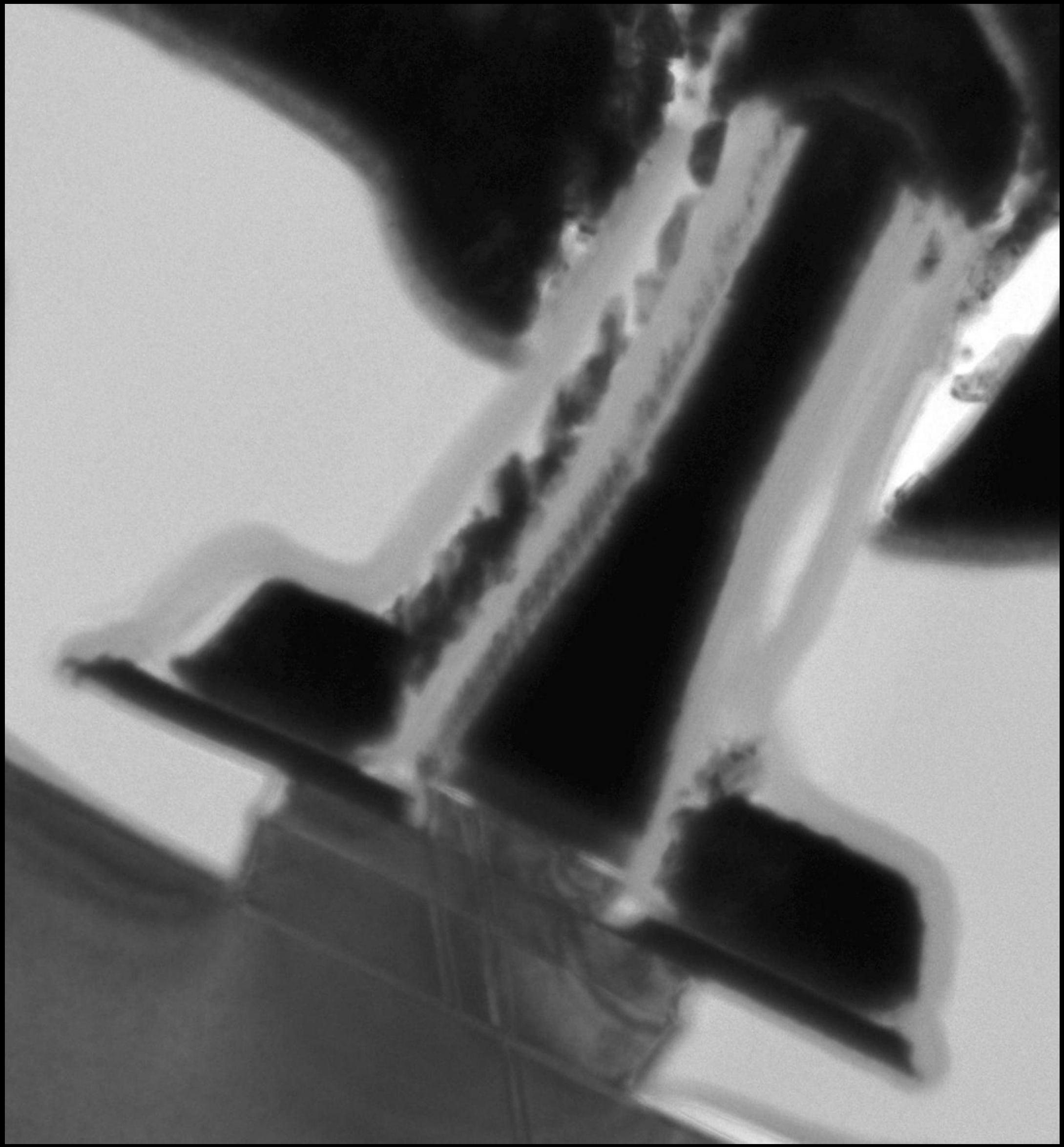
→ **Surface *doping spike 2-5nm thick.***

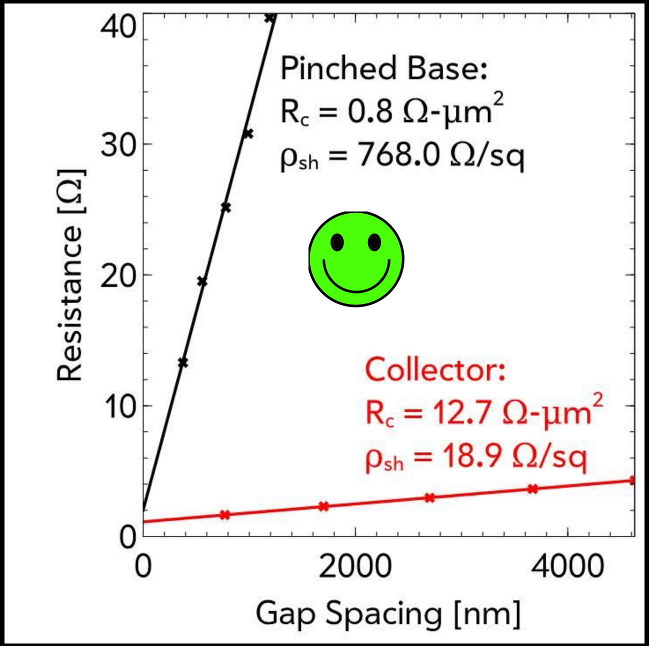
Need limited-penetration metal

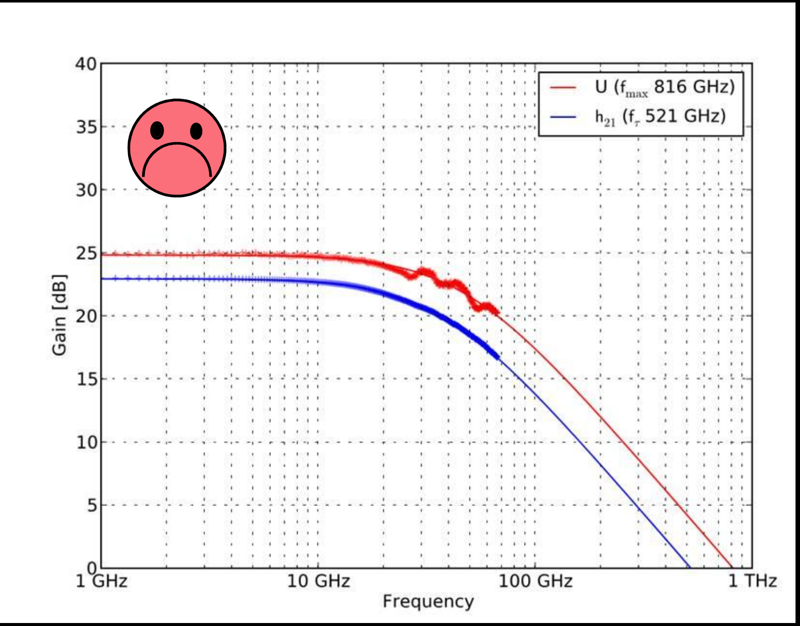
"Near-Refractory" Base Ohmic Contacts



THz InP HBTs







a few more things to fix ...

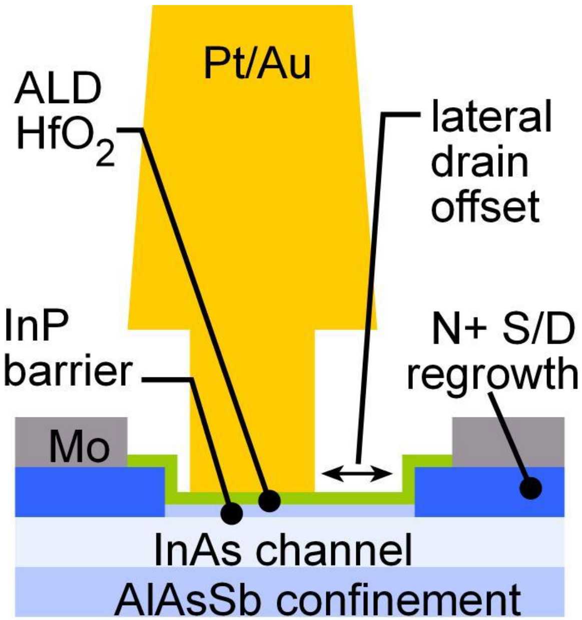
2-3 THz Field-Effect Transistors are Feasible.

3 THz FETs realized by:

Regrown low-resistivity source/drain

Very thin channels, high-K dielectrics

Gates scaled to 9 nm junctions

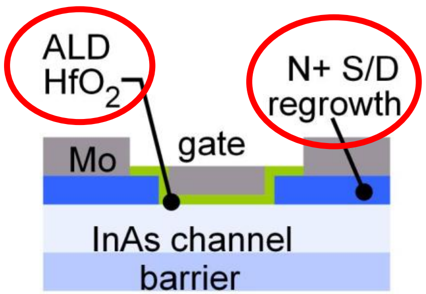


gate length	36	18	9	nm
EOT	0.8	0.4	0.2	nm
well thickness	5.6	2.8	1.4	nm
effective mass	0.05	0.08	0.08	times m_0
# bands	1	1	1	--
S/D resistivity	150	74	37	Ω-µm
extrinisic g_m	2.5	4.2	6.4	mS/µm
on-current	0.55	0.8	1.1	mA/µm
f_τ	0.70	1.2	2.0	THz
f_{max}	0.81	1.4	2.7	THz

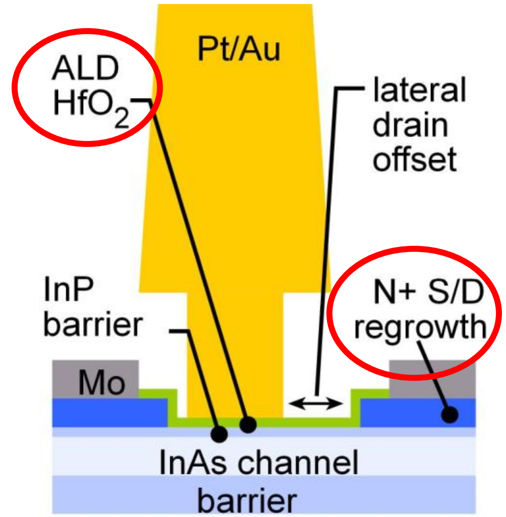
Impact:
Sensitive, low-noise receivers from 100-1000 GHz.

3 dB less noise →
need 3 dB less transmit power.

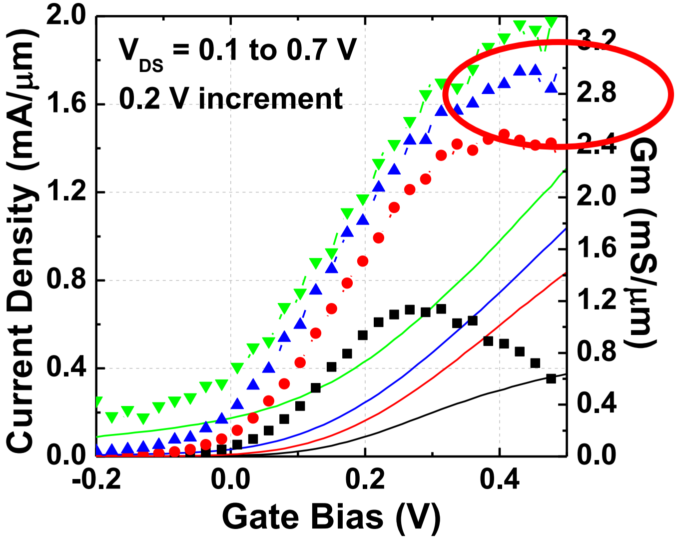
III-V MOS Development→ Benefits THz HEMTs

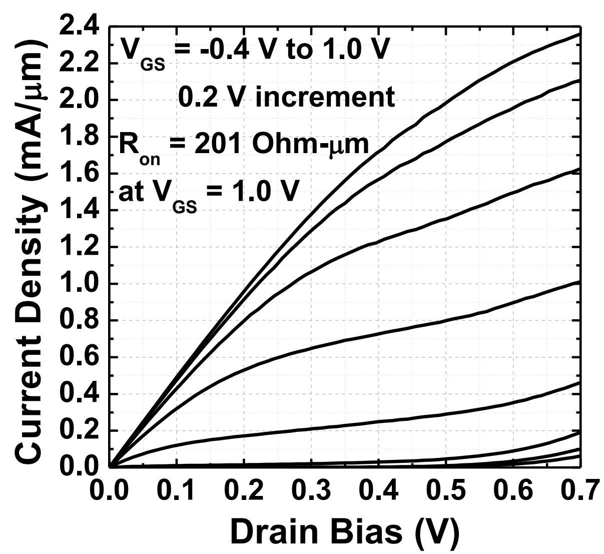


VLSI III-V MOS



THz III-V MOS

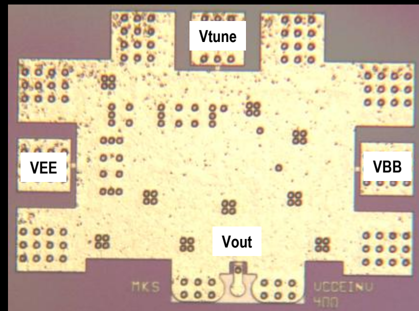




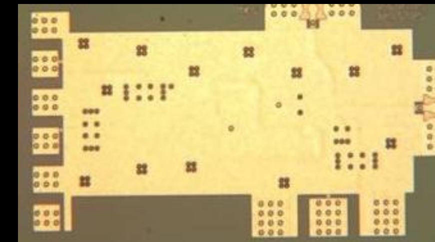
III-V MOS:
results @ 18nm L_g

InP HBT Integrated Circuits: 600 GHz & Beyond

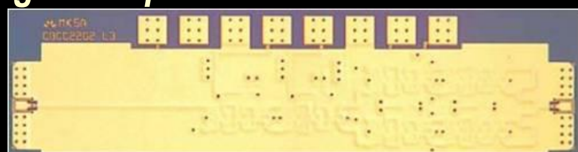
614 GHz fundamental VCO
M. Seo, TSC / UCSB



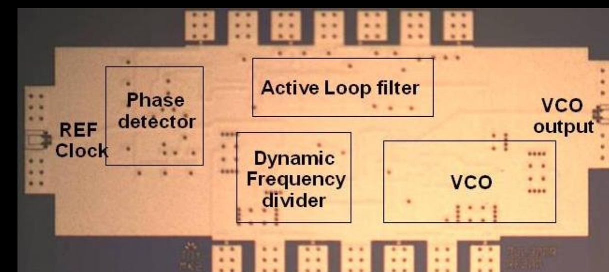
340 GHz dynamic frequency divider
M. Seo, UCSB/TSC
IMS 2010



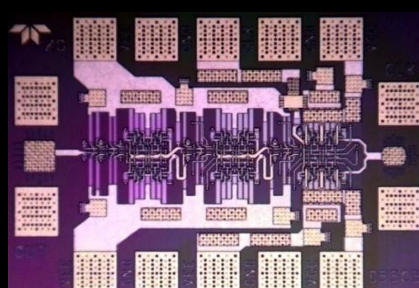
620 GHz, 20 dB gain amplifier
M Seo, TSC
IMS 2013



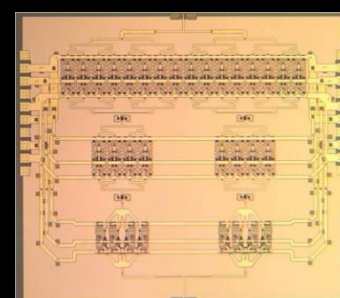
300 GHz fundamental PLL
M. Seo, TSC
IMS 2011



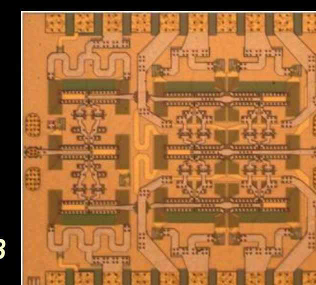
204 GHz static frequency divider (ECL master-slave latch)
Z. Griffith, TSC
CSIC 2010



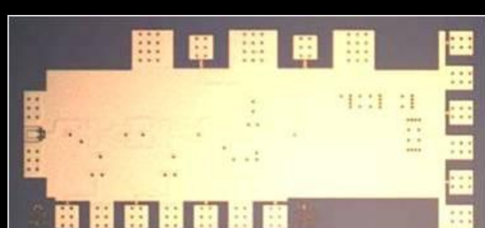
220 GHz 180 mW power amplifier
T. Reed, UCSB
CSICS 2013



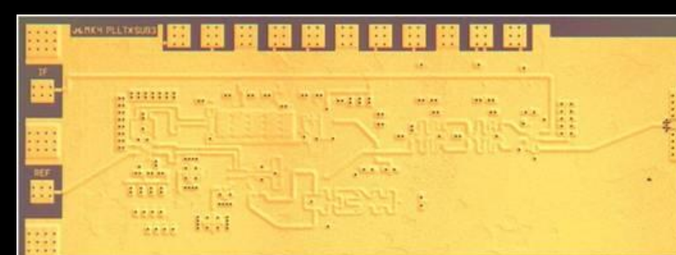
81 GHz 470 mW power amplifier
H-C Park UCSB
IMS 2014



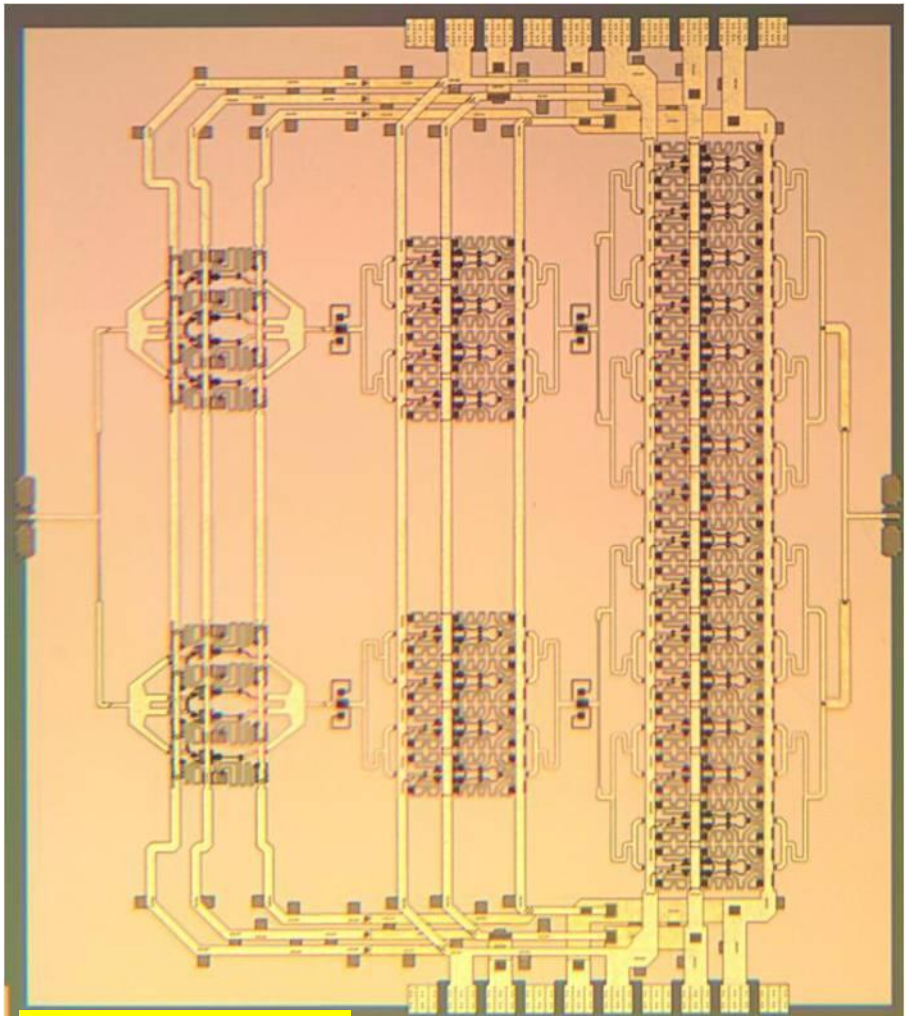
Integrated 300/350GHz Receivers:
LNA/Mixer/VCO
M. Seo TSC



600 GHz Integrated Transmitter
PLL + Mixer
M. Seo TSC

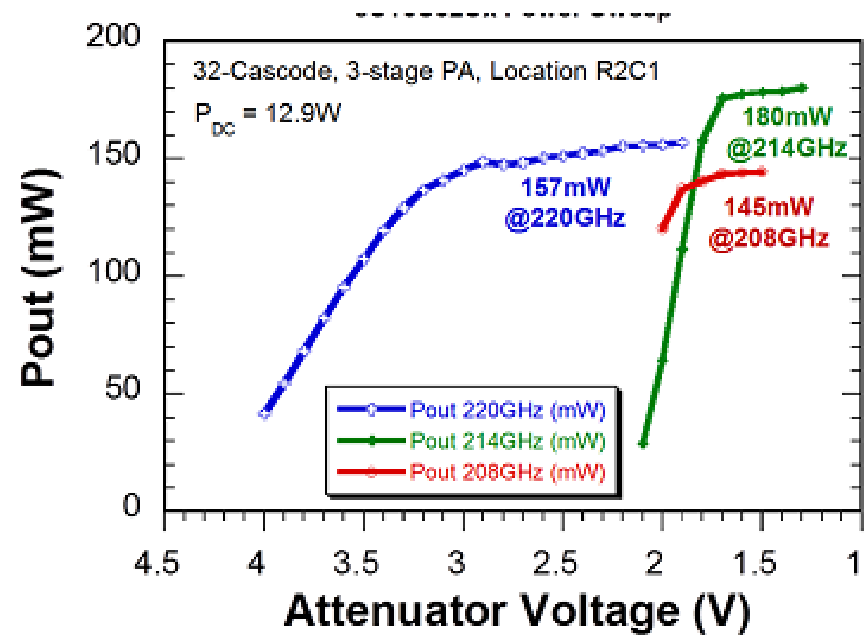


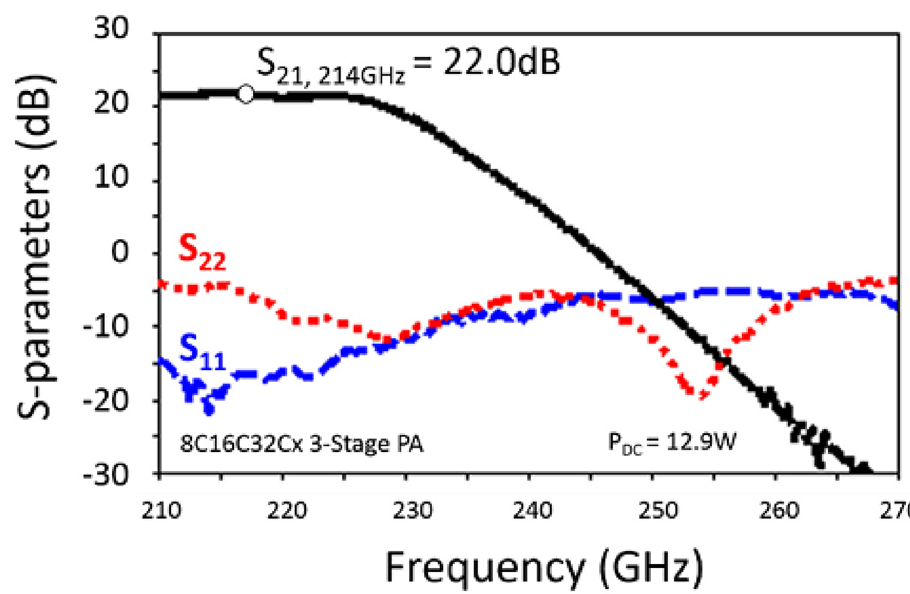
220 GHz 180mW Power Amplifier (330 mW design)



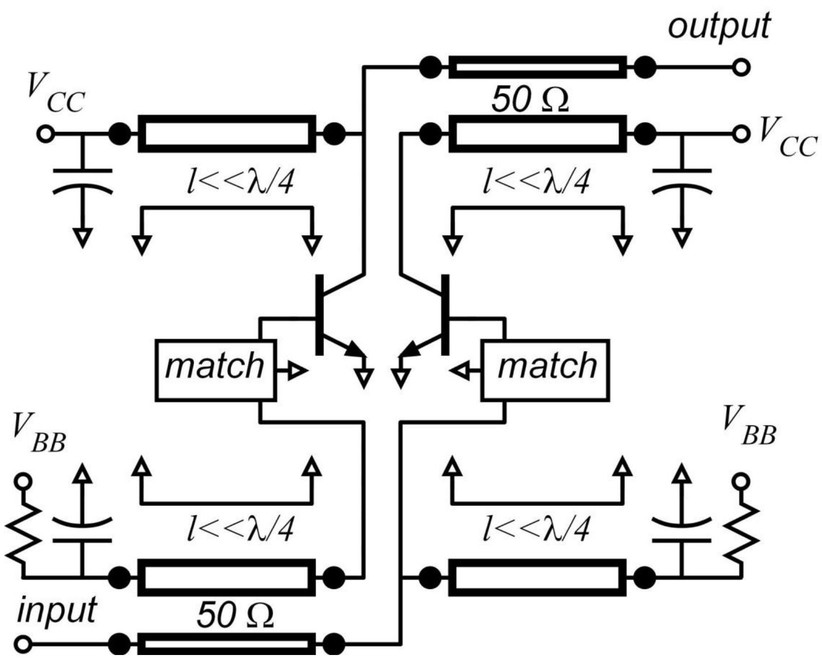
2.3 mm x 2.5 mm

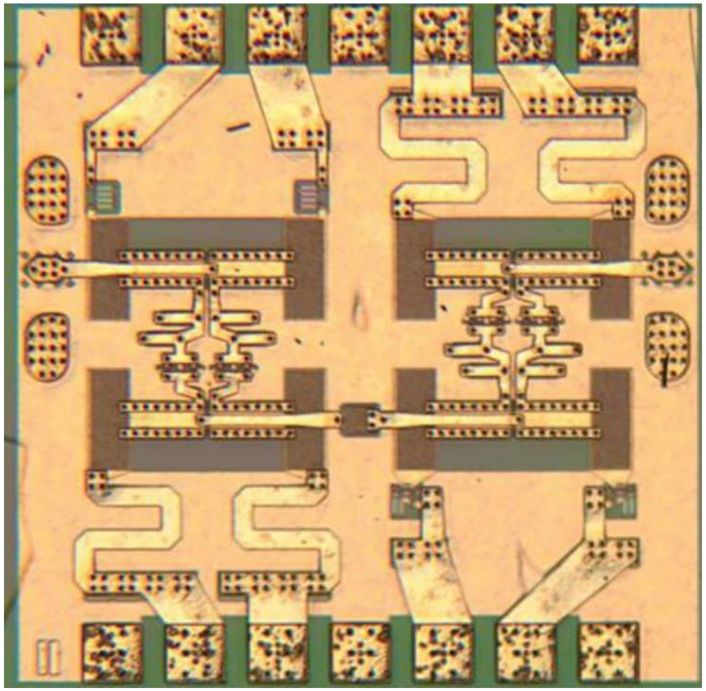
T. Reed, UCSB
Z. Griffith, Teledyne
Teledyne 250 nm InP HBT



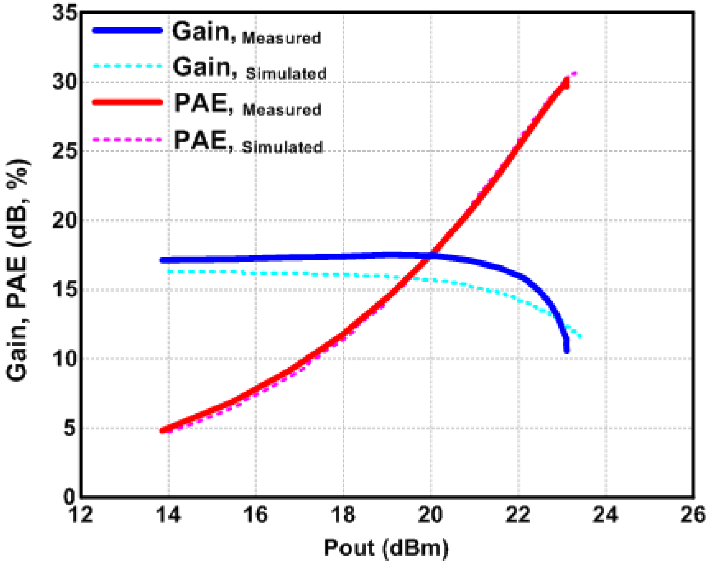


PAs using **Sub-λ/4** Baluns for Series-Combining





Park *et al*, 2013 CSICS



80-90 GHz Power Amplifier

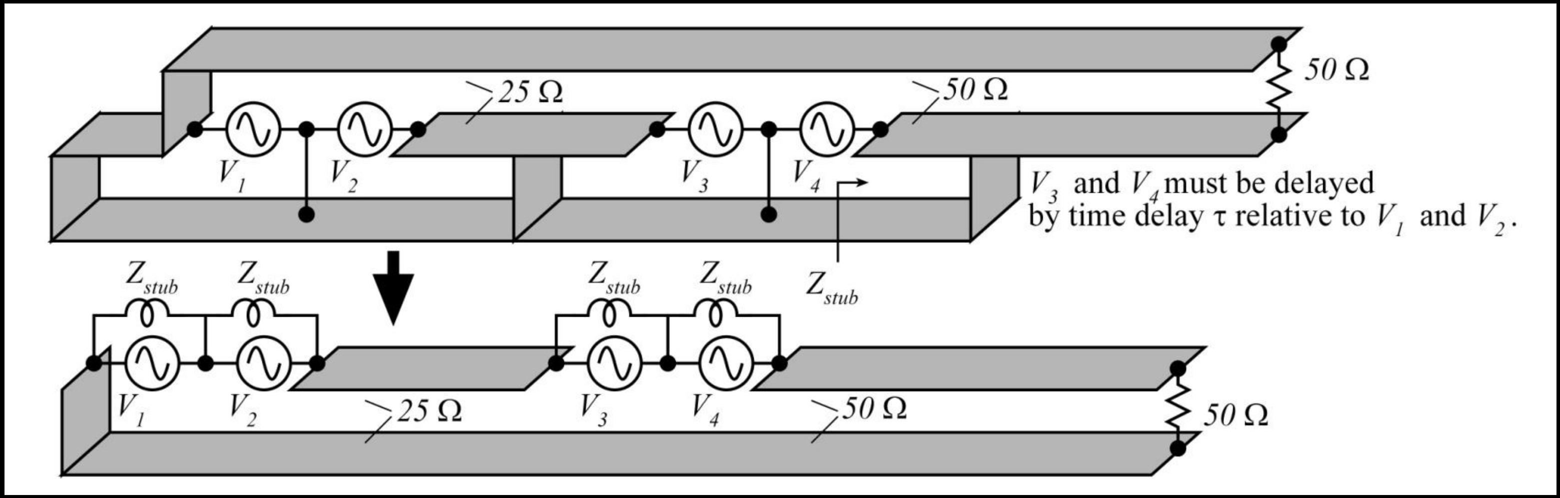
17.5dB Gain, >200mW P_{SAT}, >30% PAE

Power per unit IC die area*
=307 mW/mm² (pad area included)
=497 mW/mm² (if pad area not included)

to be presented, 2014 IEEE IMS:

An 81GHz, 470mW, 1.1mm^2 InP HBT Power Amplifier with 4:1 Series Power Combining using Sub-quarter-wavelength Baluns

Hyun-chul Park, Student Member, IEEE, Saeid Daneshgar, and Zach Griffith, Miguel Urteaga, Byung-sung Kim, Member, IEEE, and Mark J. W. Rodwell, Fellow, IEEE



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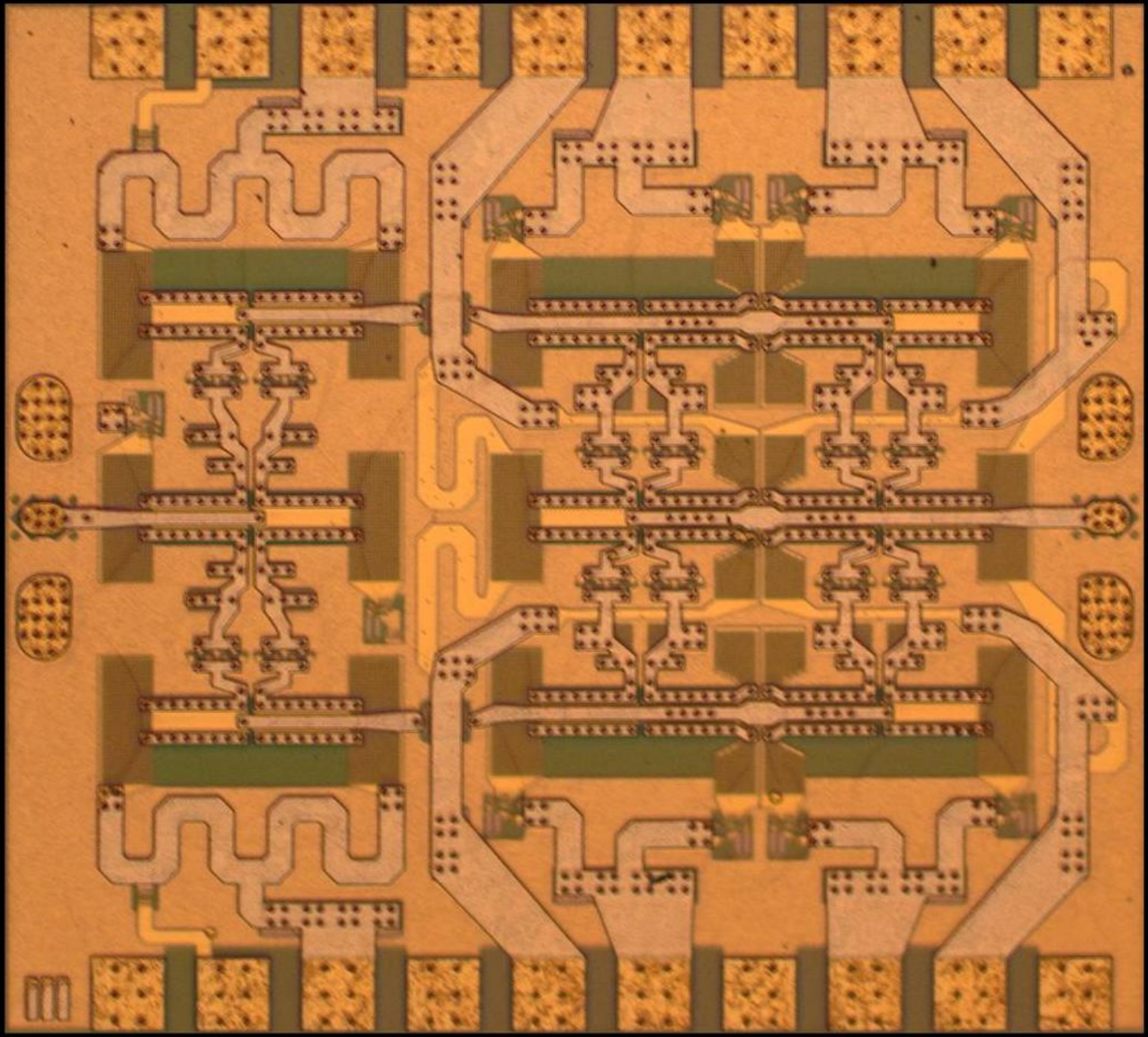
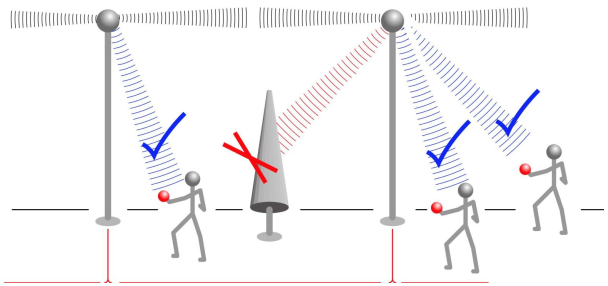
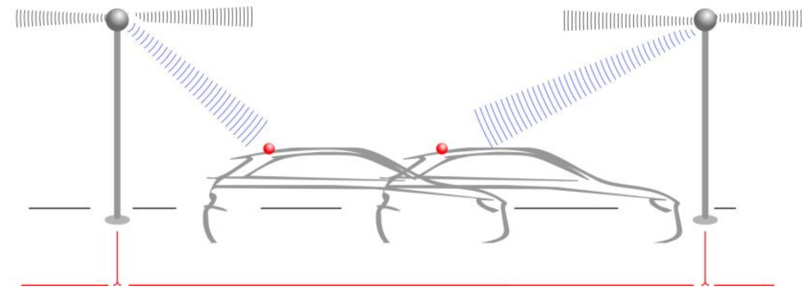


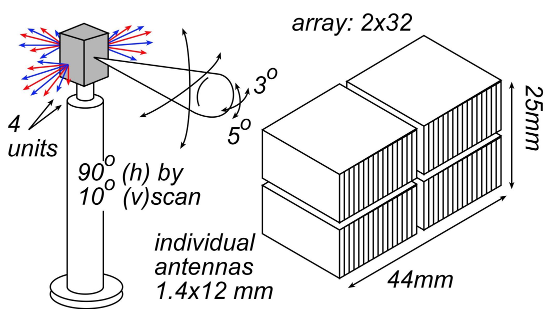
50-500 GHz Wireless Electronics

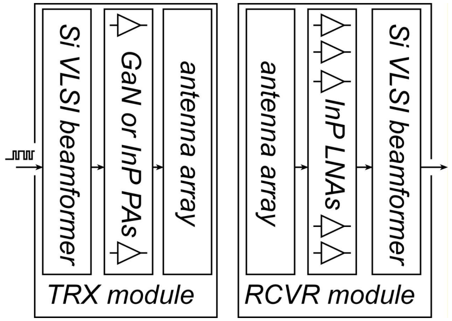
Mobile communication @ 2Gb/s per user, 1 Tb/s per base station





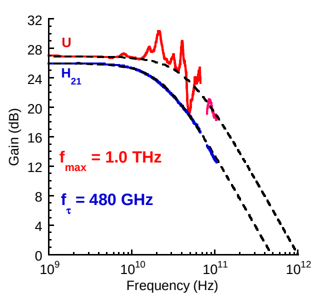
Requires: large arrays, complex signal processing, high P_{out}, low F_{min}

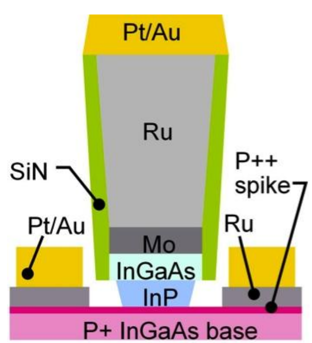


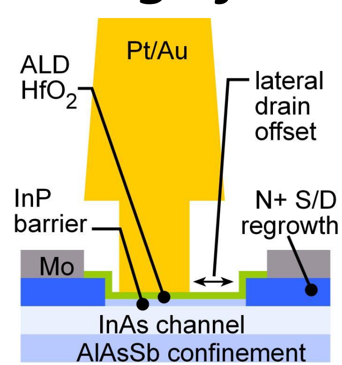


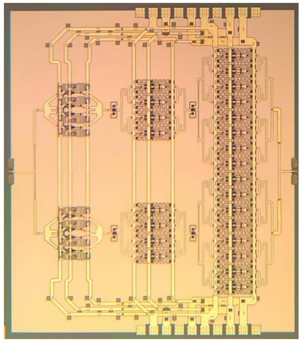
VLSI beamformers
VLSI equalizers
III-V LNAs & PAs

III-V Transistors will perform well enough for 1.5-2 THz systems.



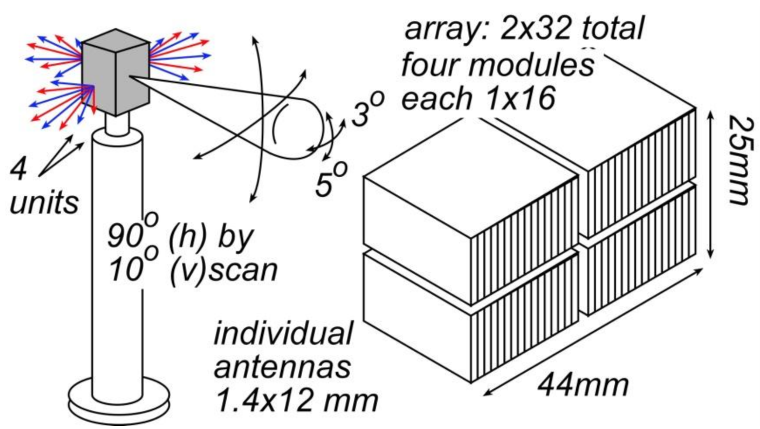






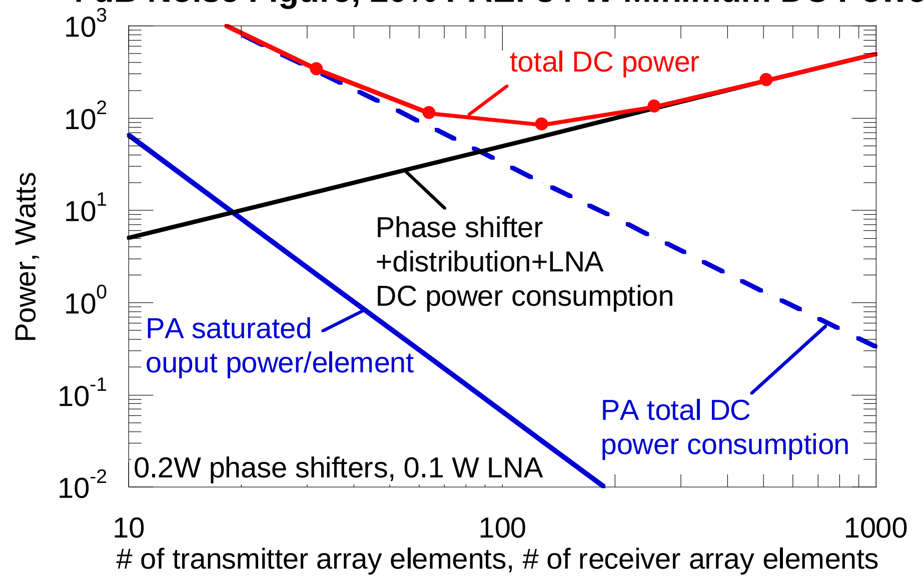
(backup slides follow)

Effects of array size, Transmitter PAE, Receiver F_{min}



200 mW phase shifters in TRX & RCVR, 0.1 W LNAs

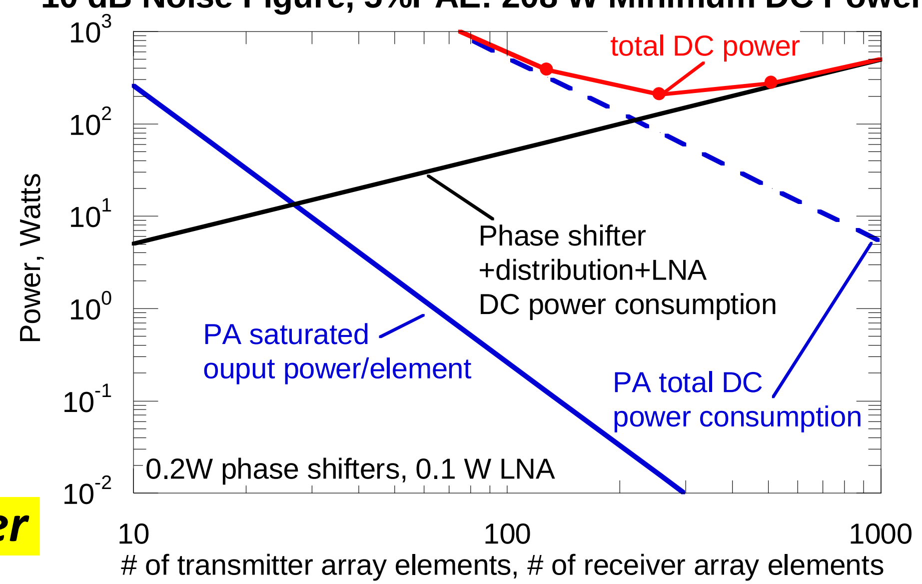
4 dB Noise Figure, 20% PAE: 84 W Minimum DC Power



Large arrays:
  more directivity, more complex ICs
Small arrays:
  less directivity, less complex ICs

→ *Proper array size minimizes DC power*

10 dB Noise Figure, 5%PAE: 208 W Minimum DC Power

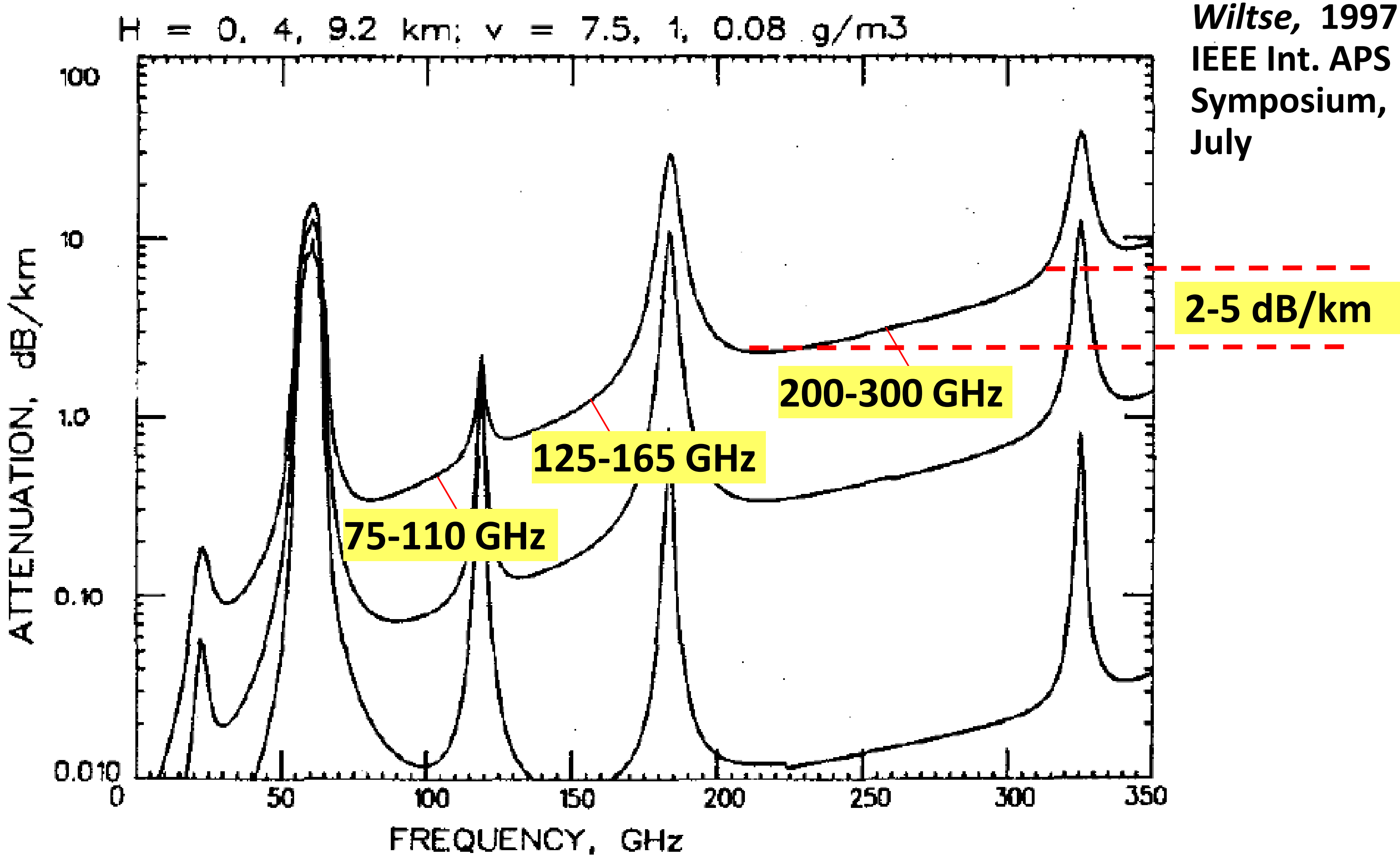


Low transmitter PAE
& high receiver noise
are partially offset using arrays,

but DC power, system complexity still suffer

50-500 GHz Wireless Has Low Attenuation ?

Wiltse, 1997
IEEE Int. APS Symposium, July



Low attenuation on a sunny day